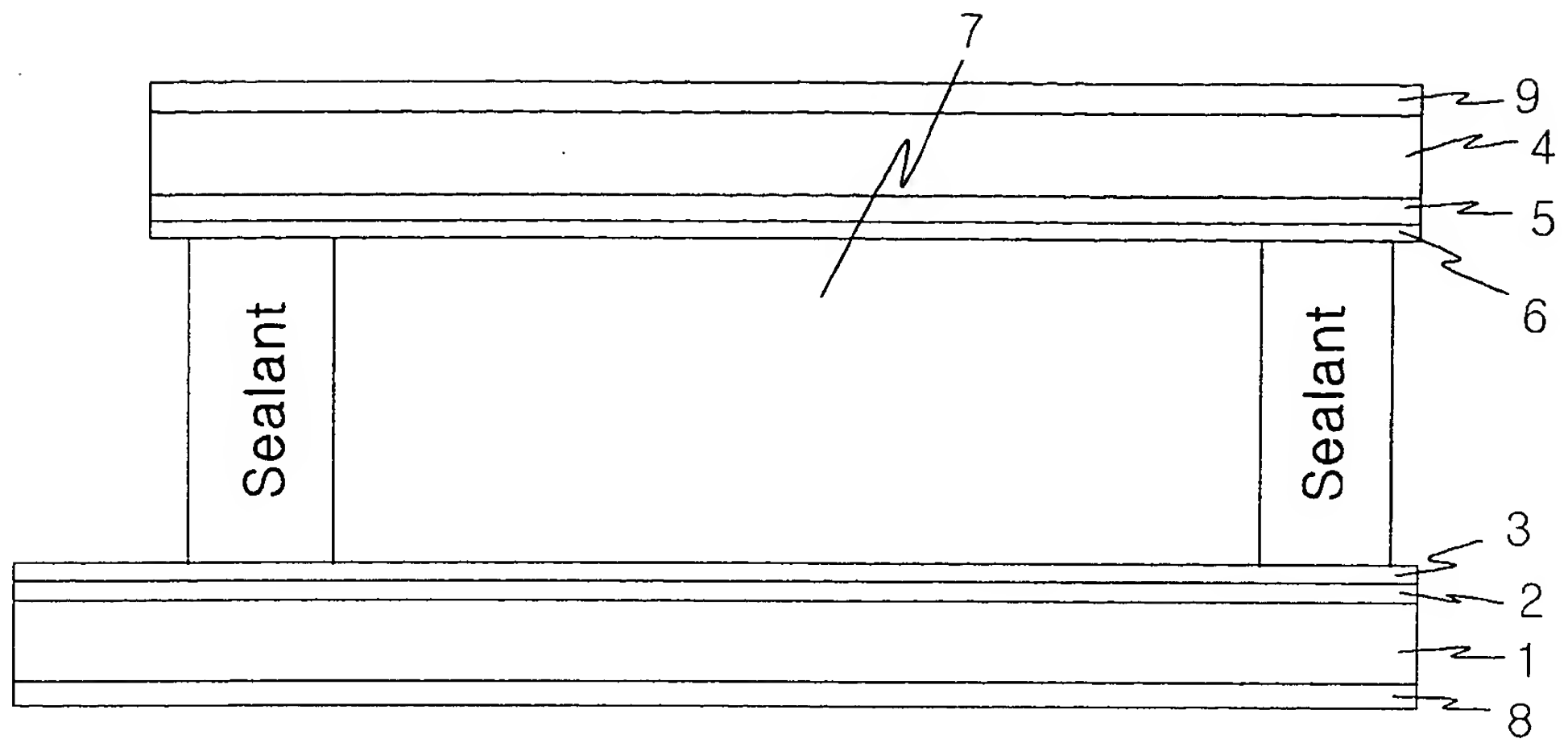
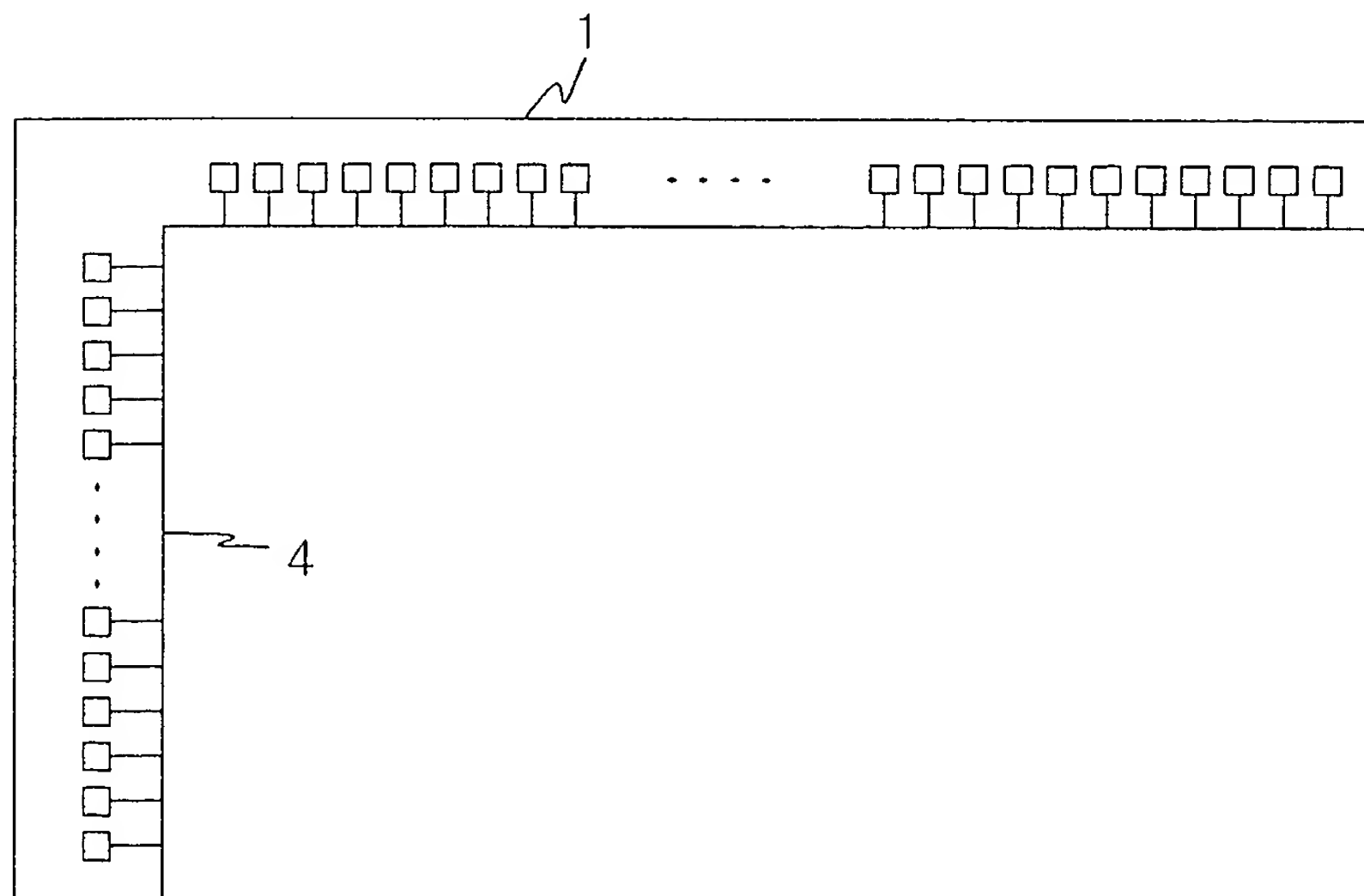


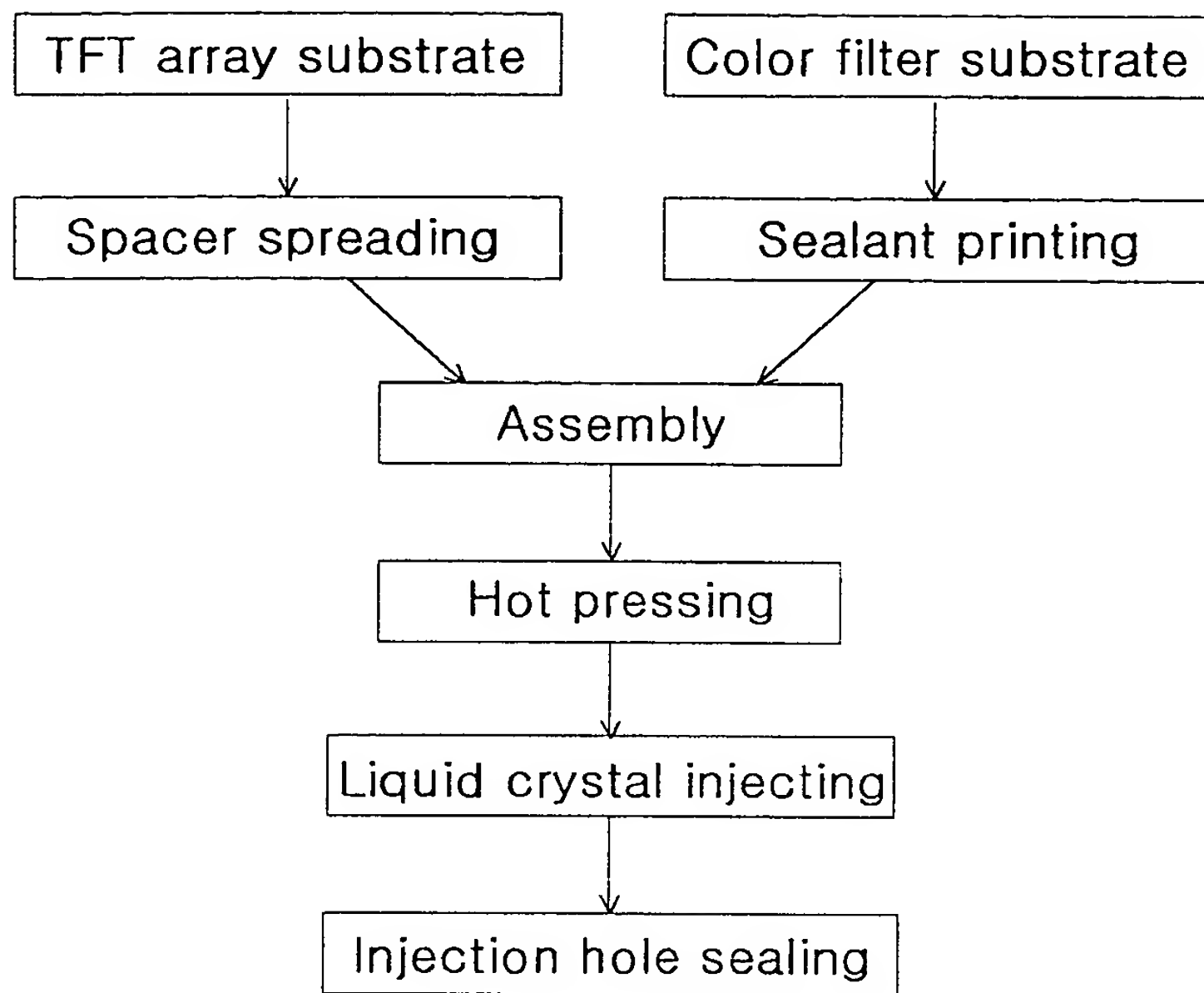
*FIG.1*



*FIG.2*



*FIG.3*



*FIG.4*

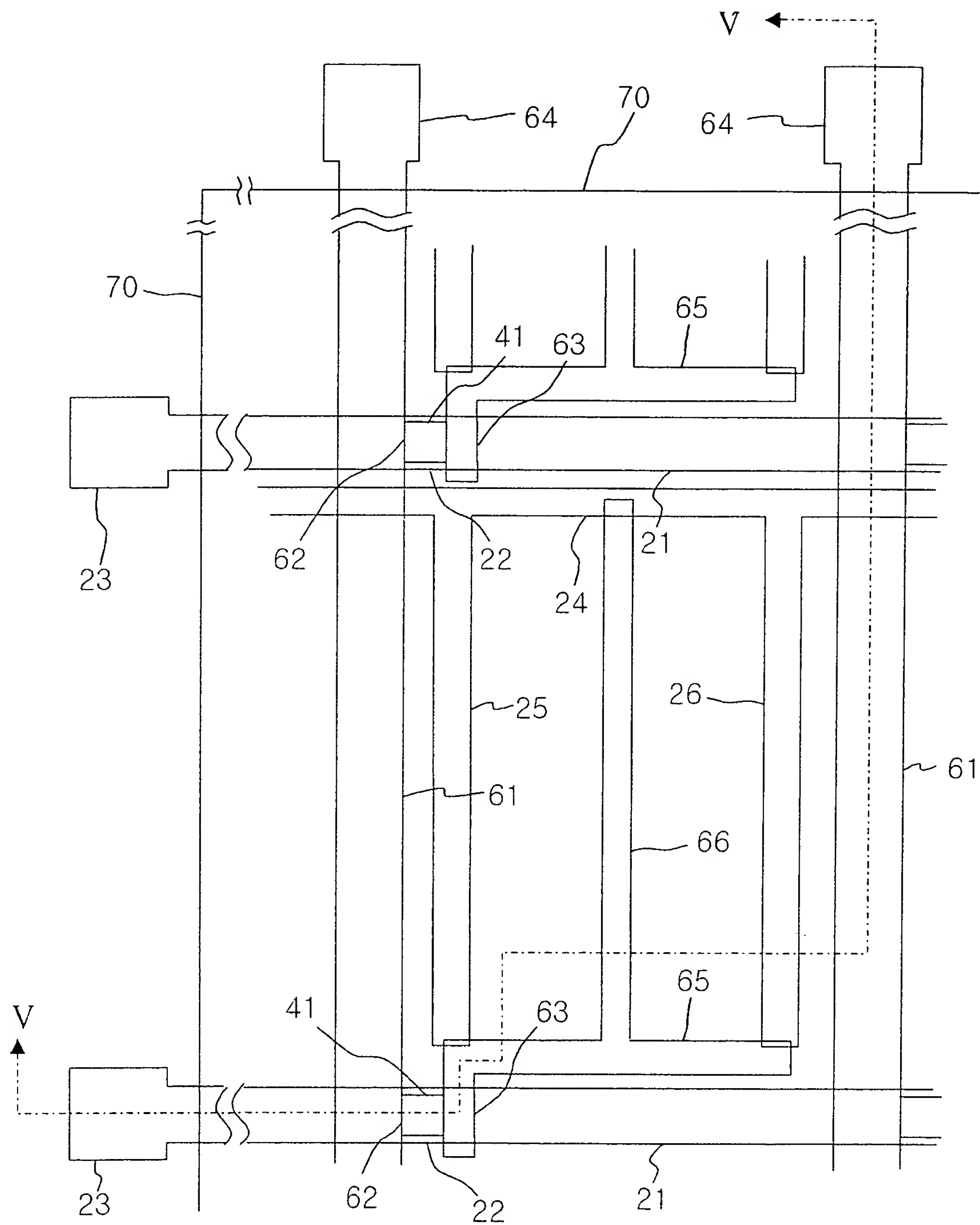
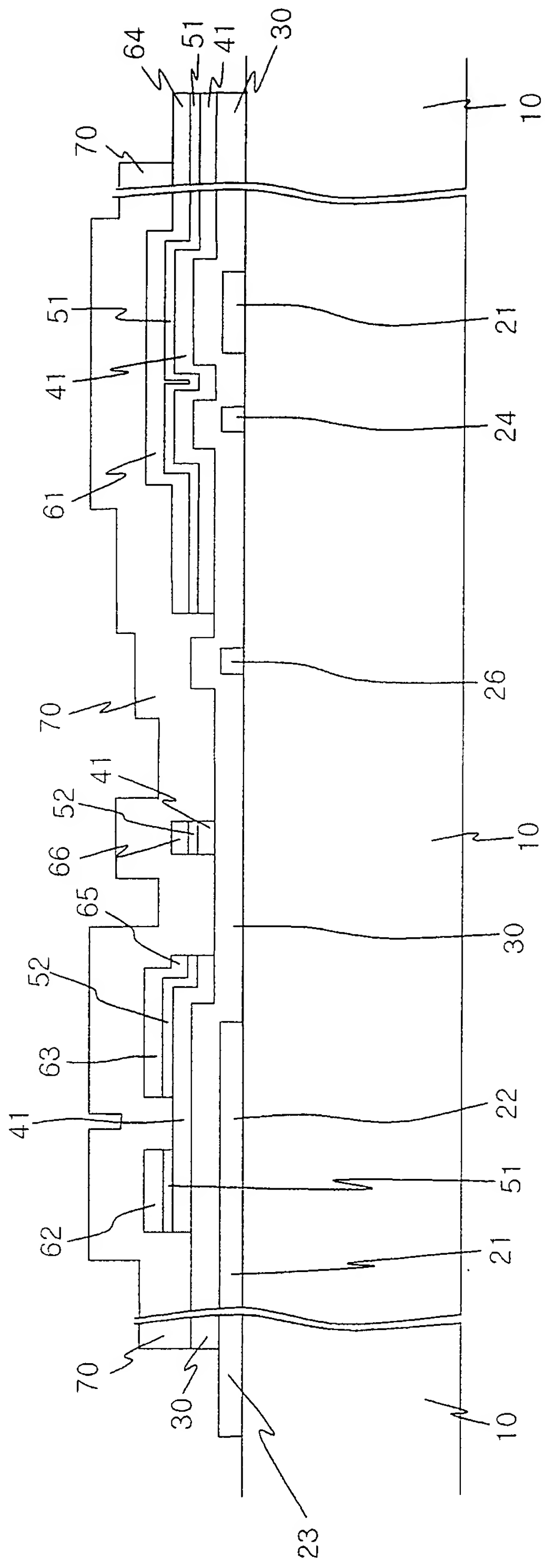


FIG.5



*FIG. 6A*

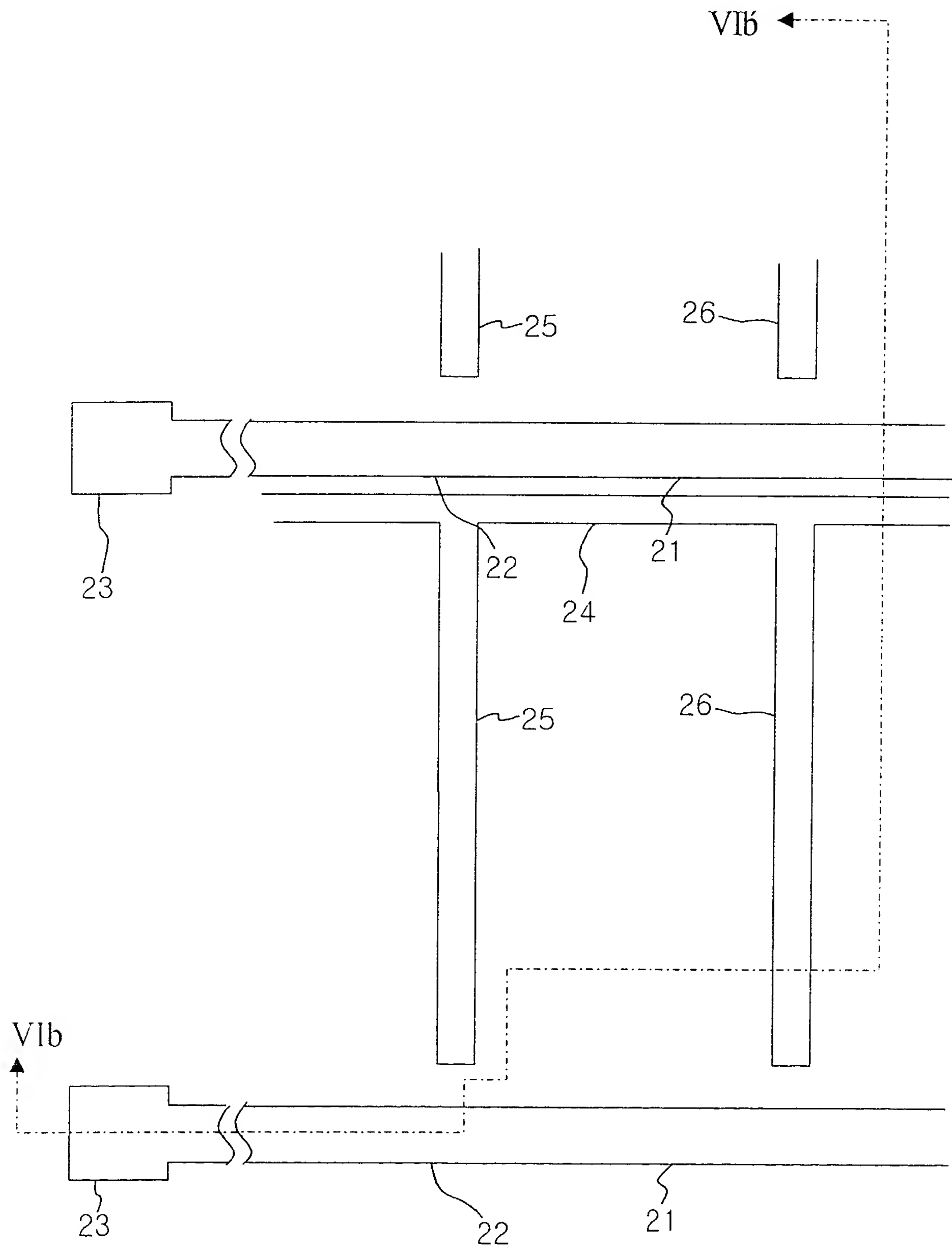


FIG.6B

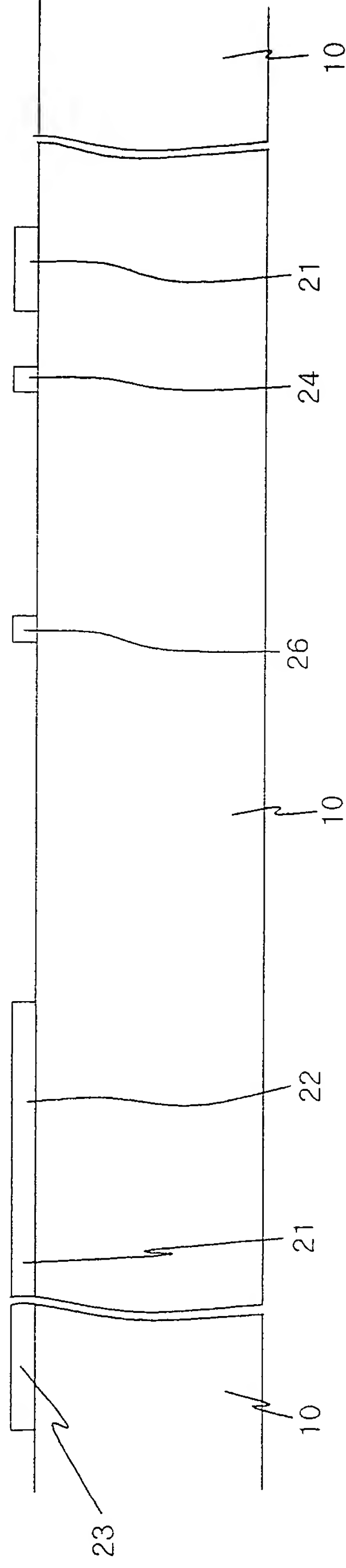


FIG. 7A

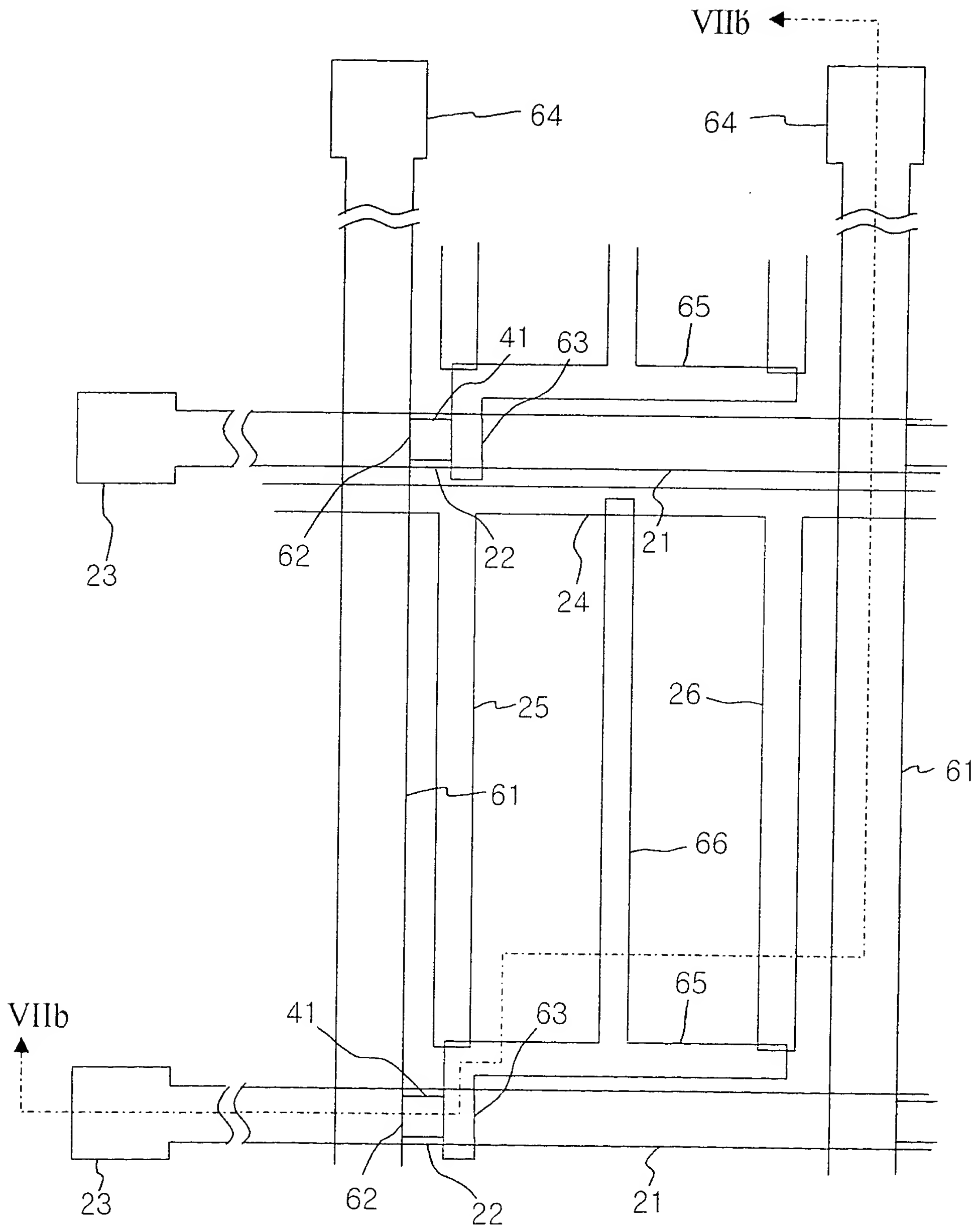


FIG.7B

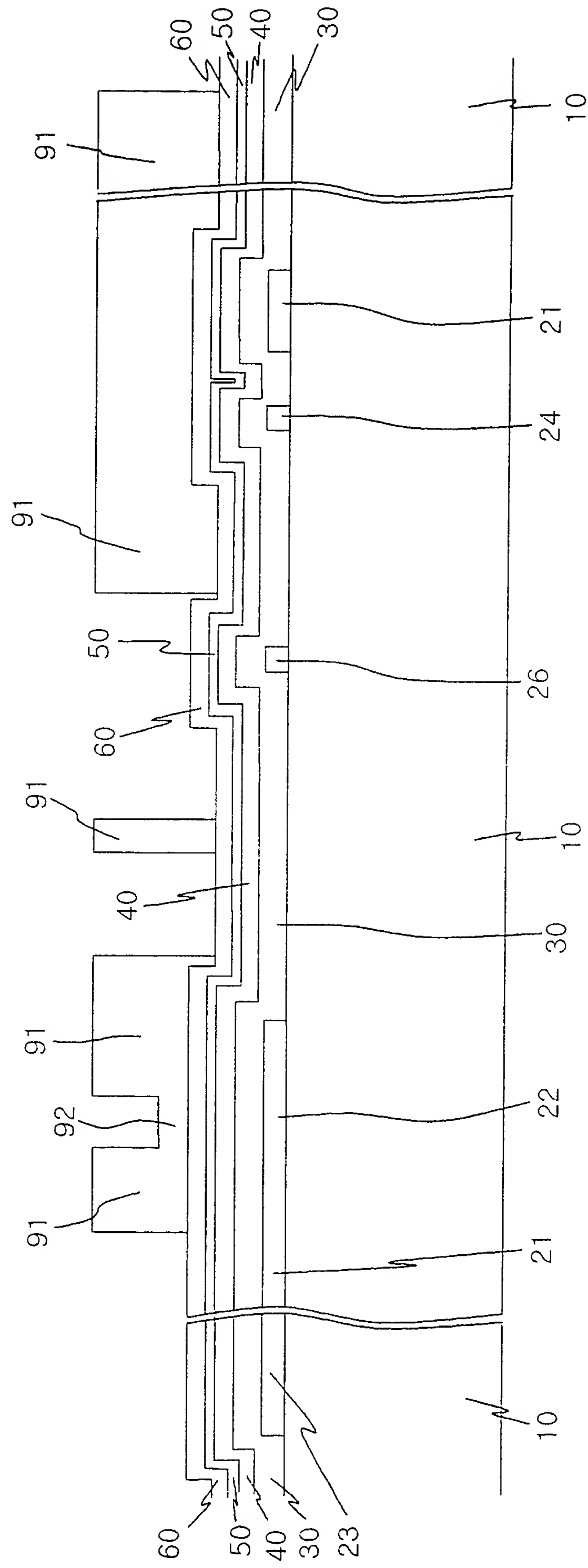




FIG.8

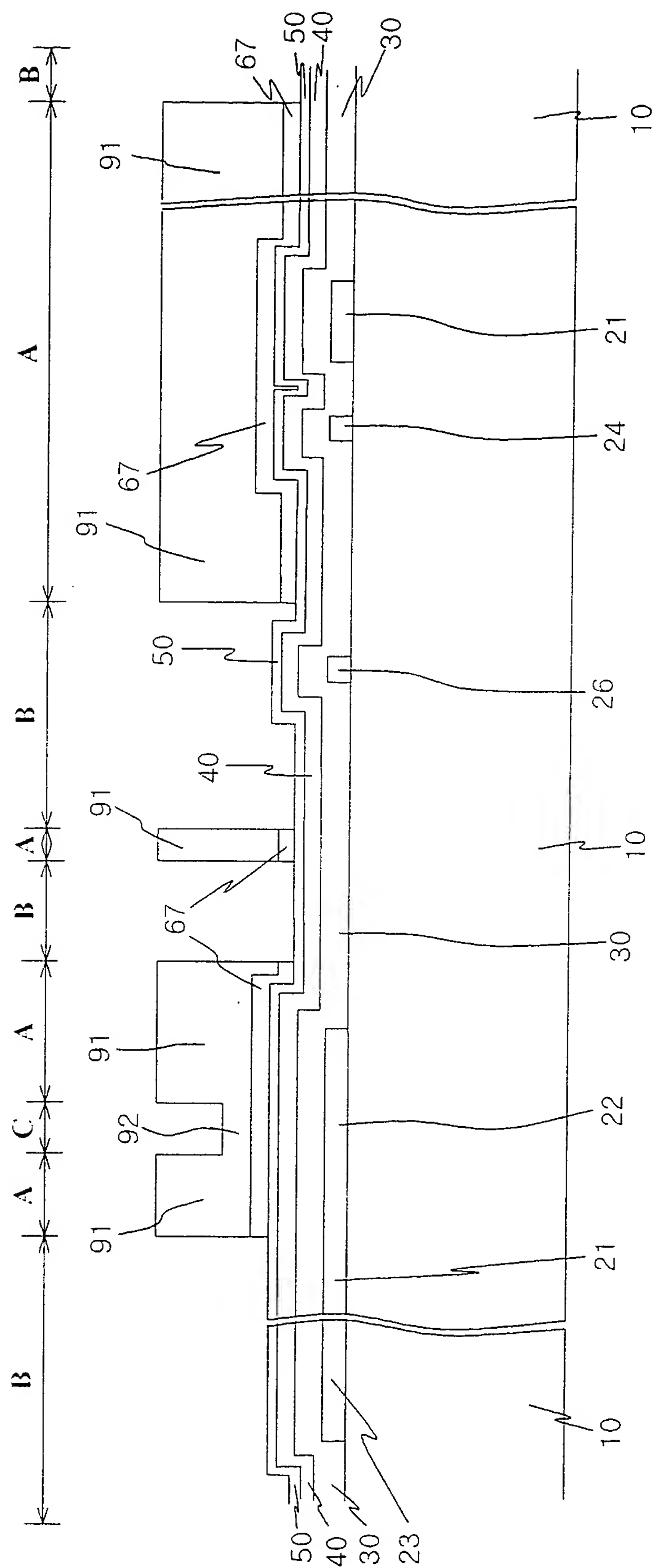


FIG.9

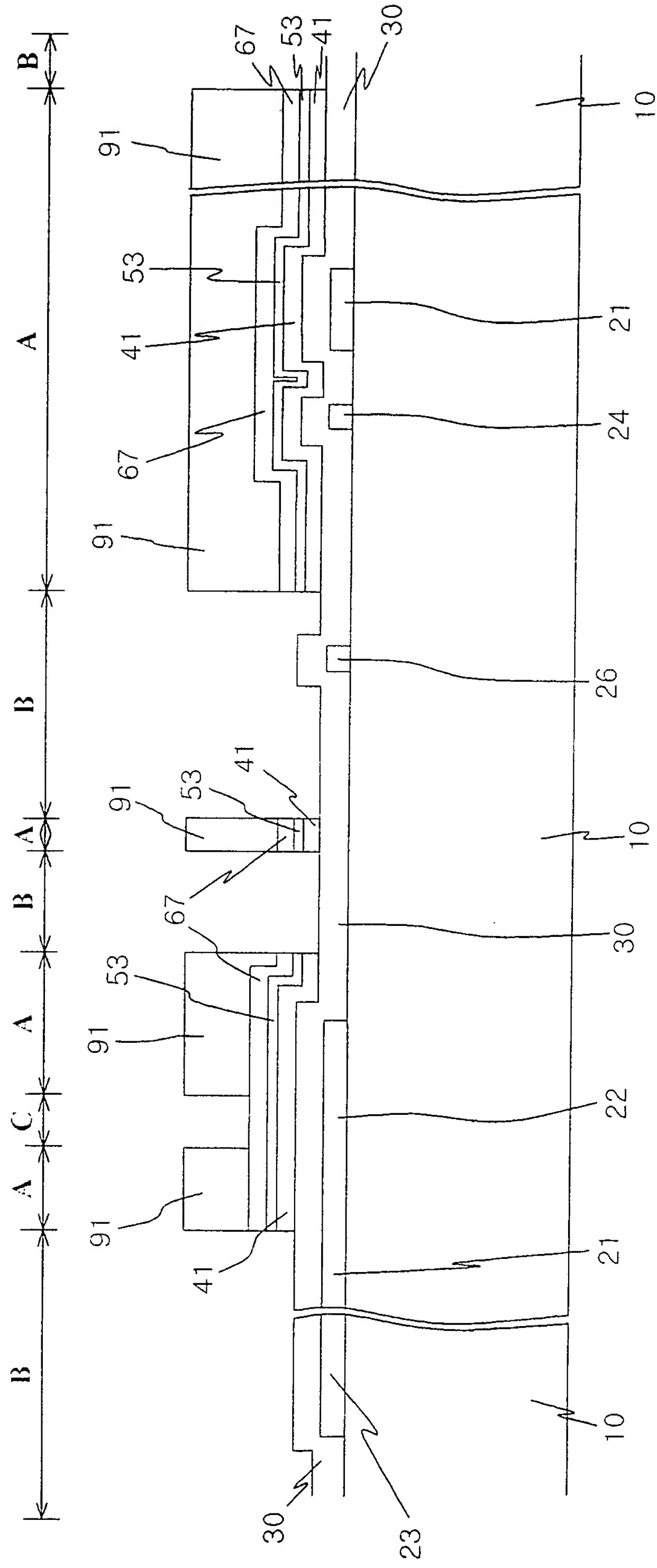


FIG.10

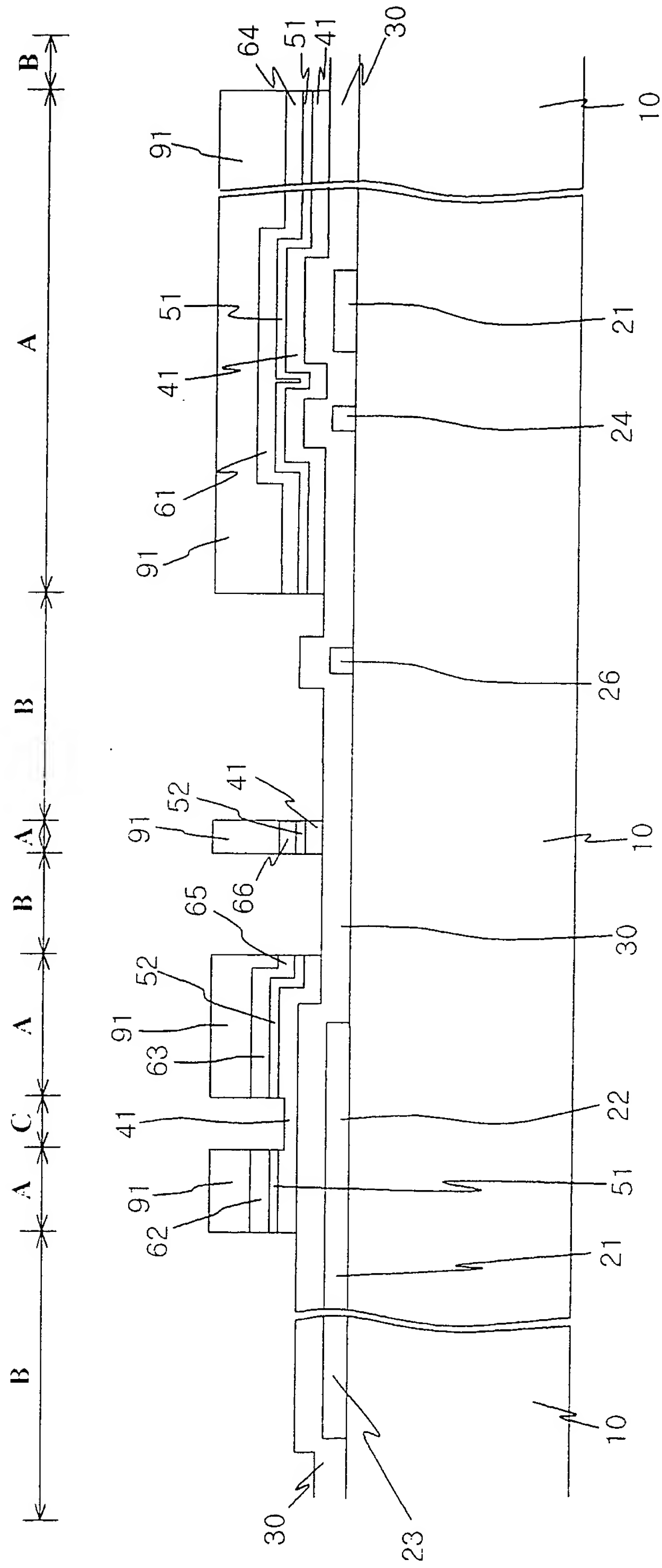


FIG. 11

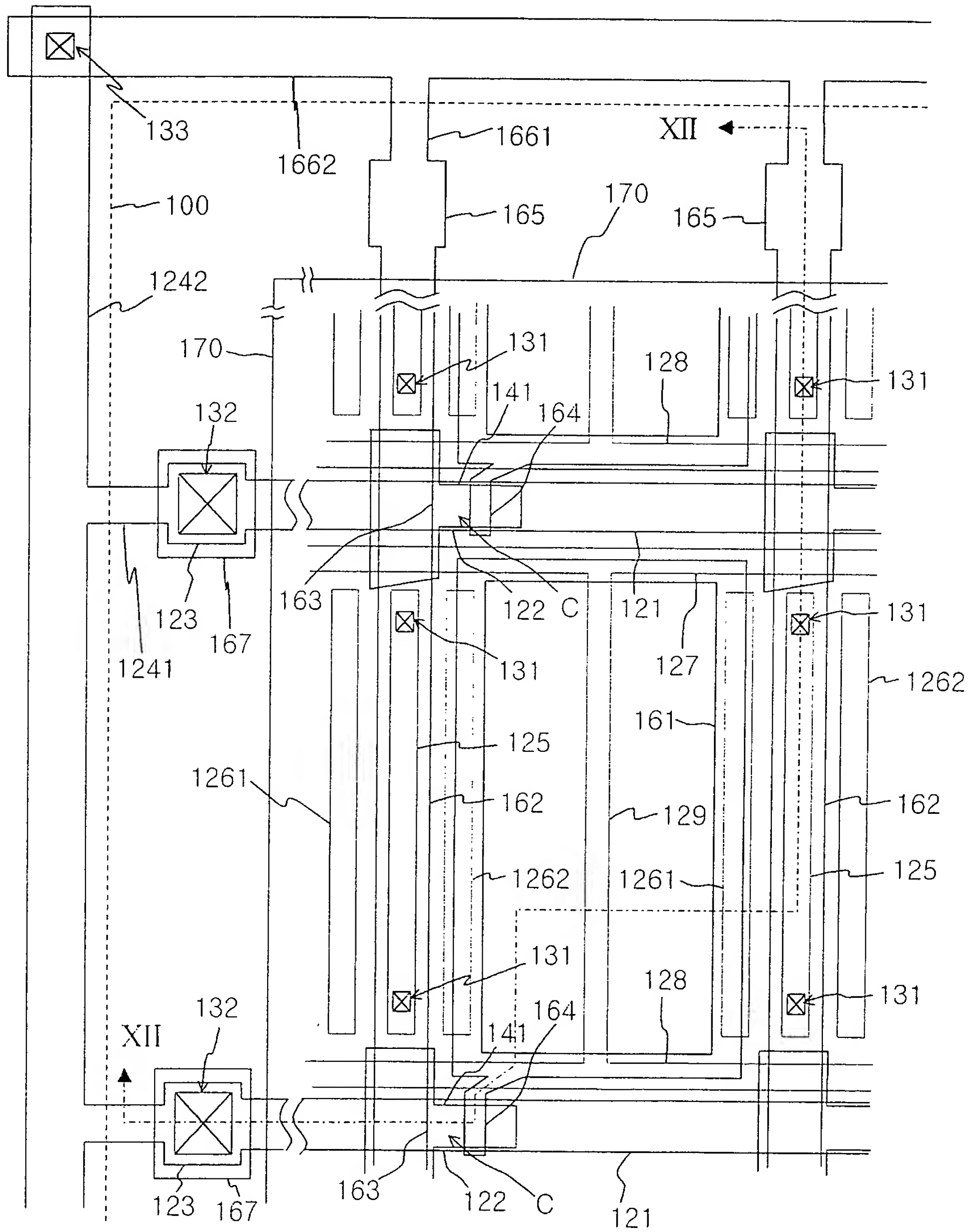


FIG.12

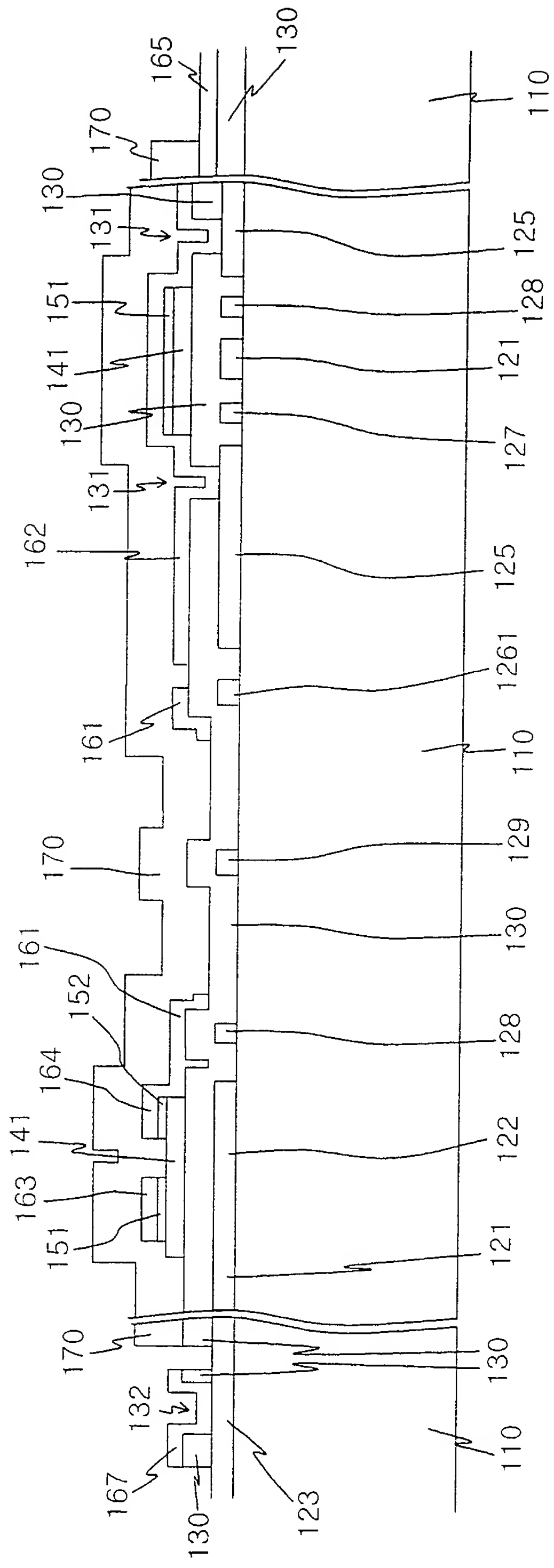


FIG. 13B is a cross-sectional view of a semiconductor device. The device is divided into two main sections by a central horizontal line. The top section shows a series of vertical structures 125 and 126, with horizontal structures 121, 122, and 123. The bottom section shows a similar structure with vertical structures 125 and 126, and horizontal structures 121, 122, and 123. A dashed line labeled XIIIb indicates a cross-section through the device.

FIG. 13B

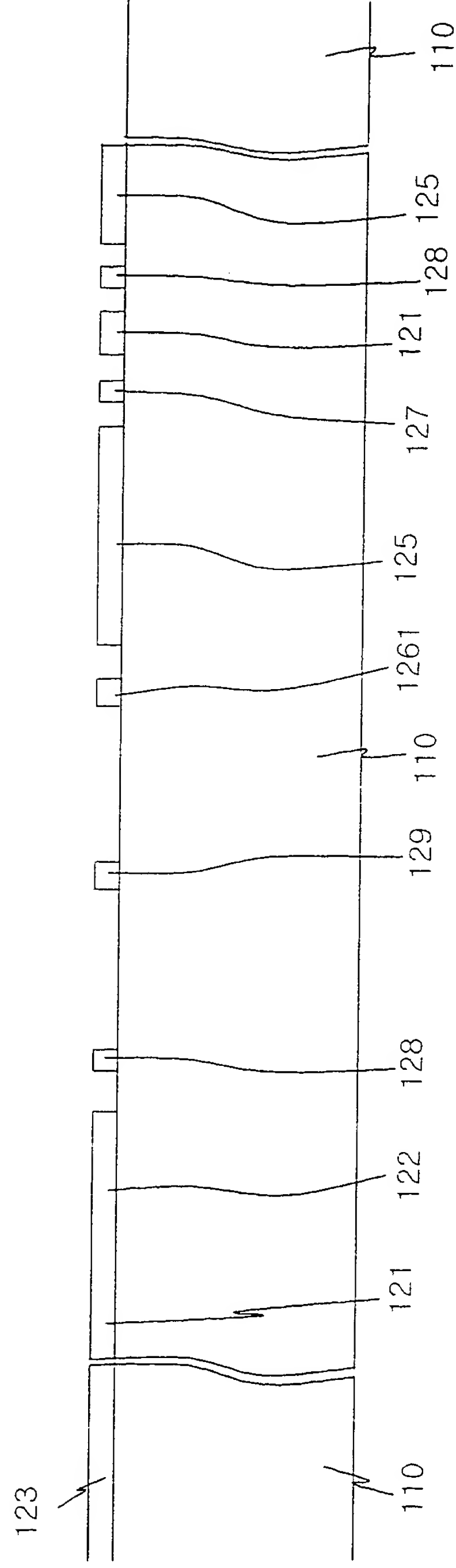
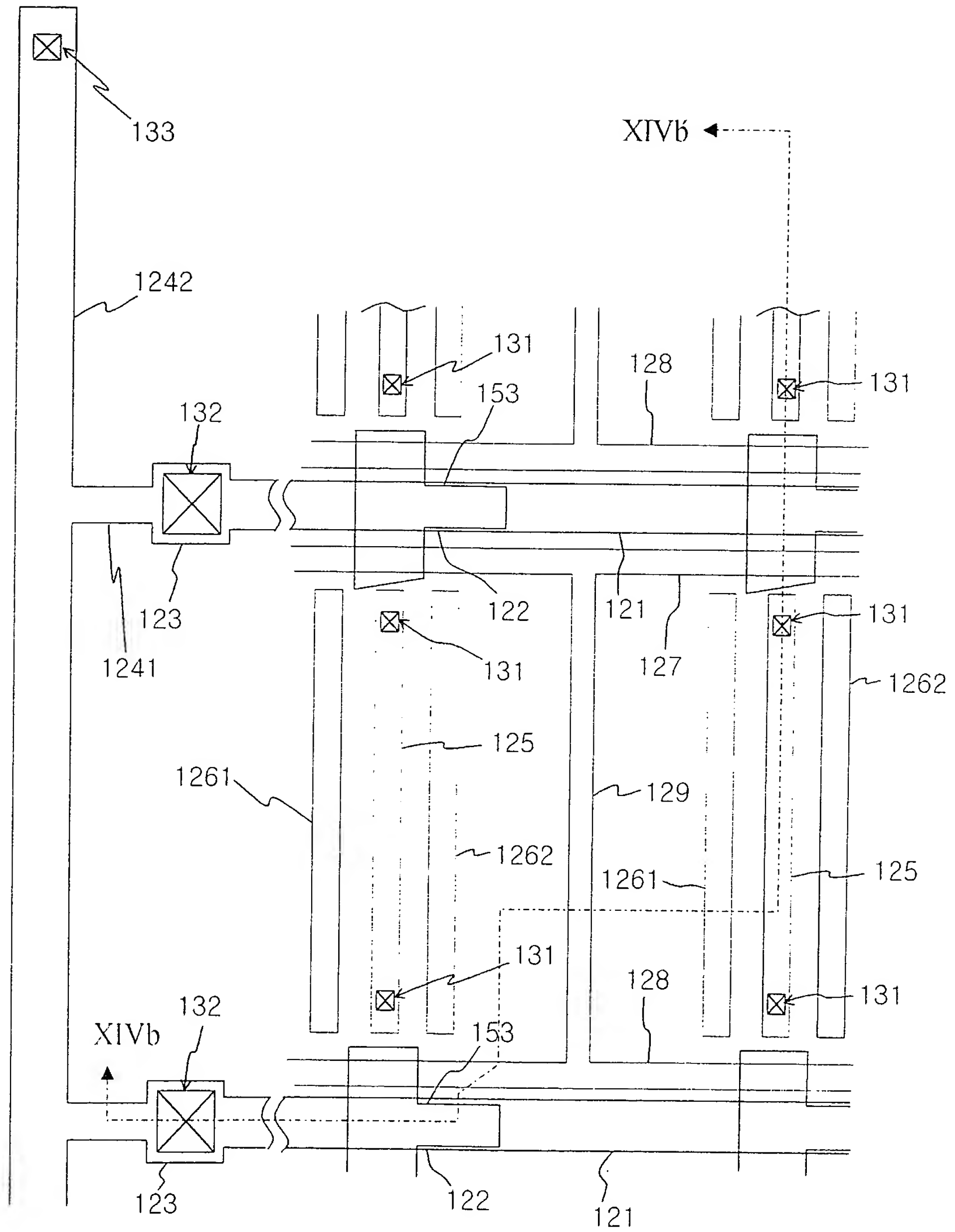


FIG.14A





**FIG. 14B**

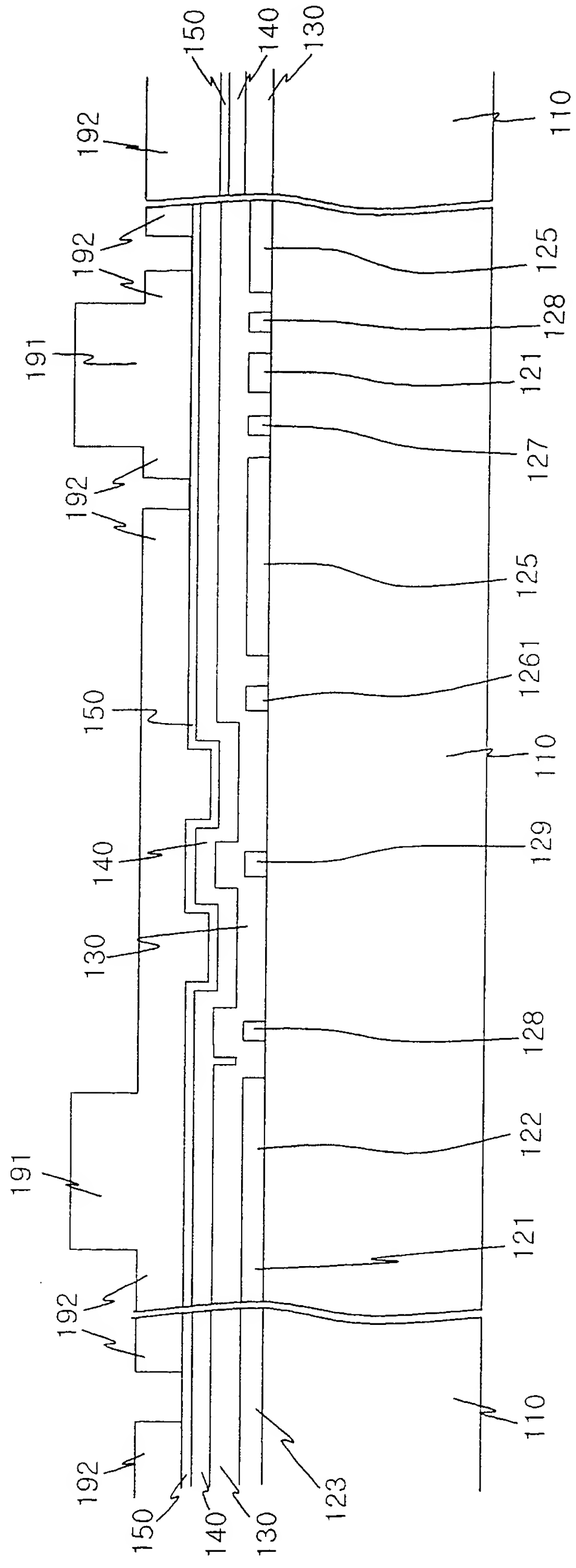


FIG.15

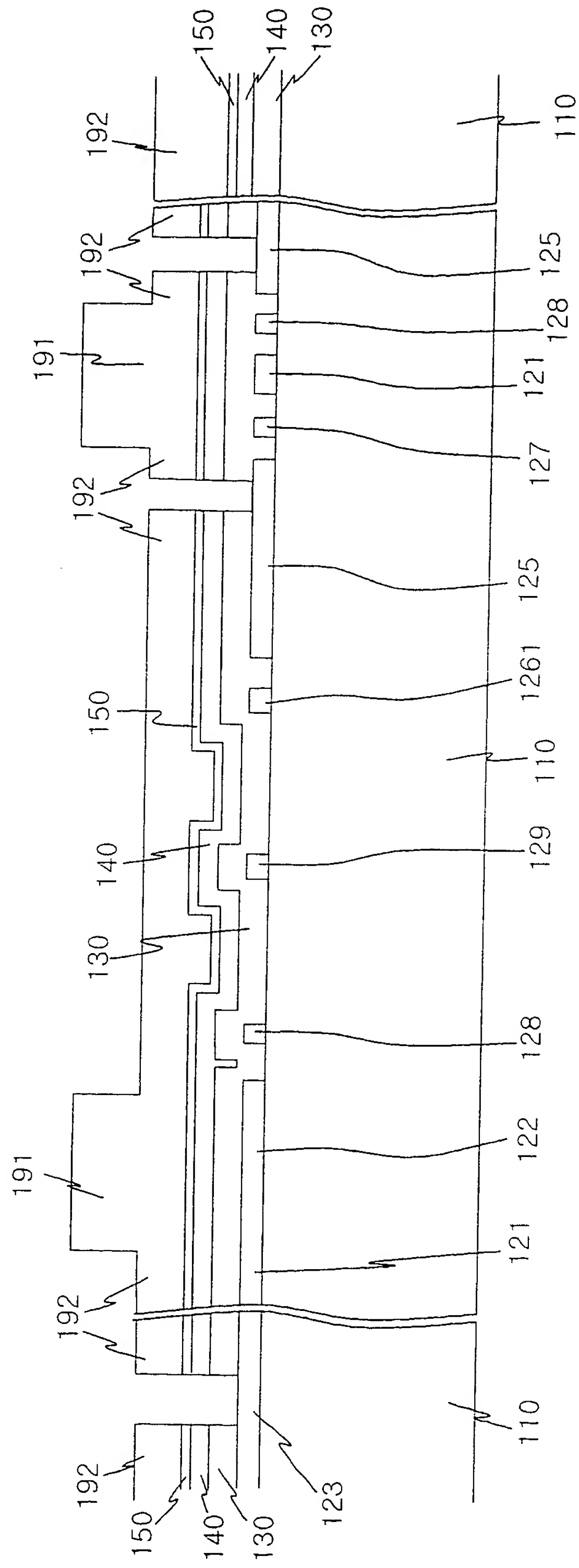


FIG.16

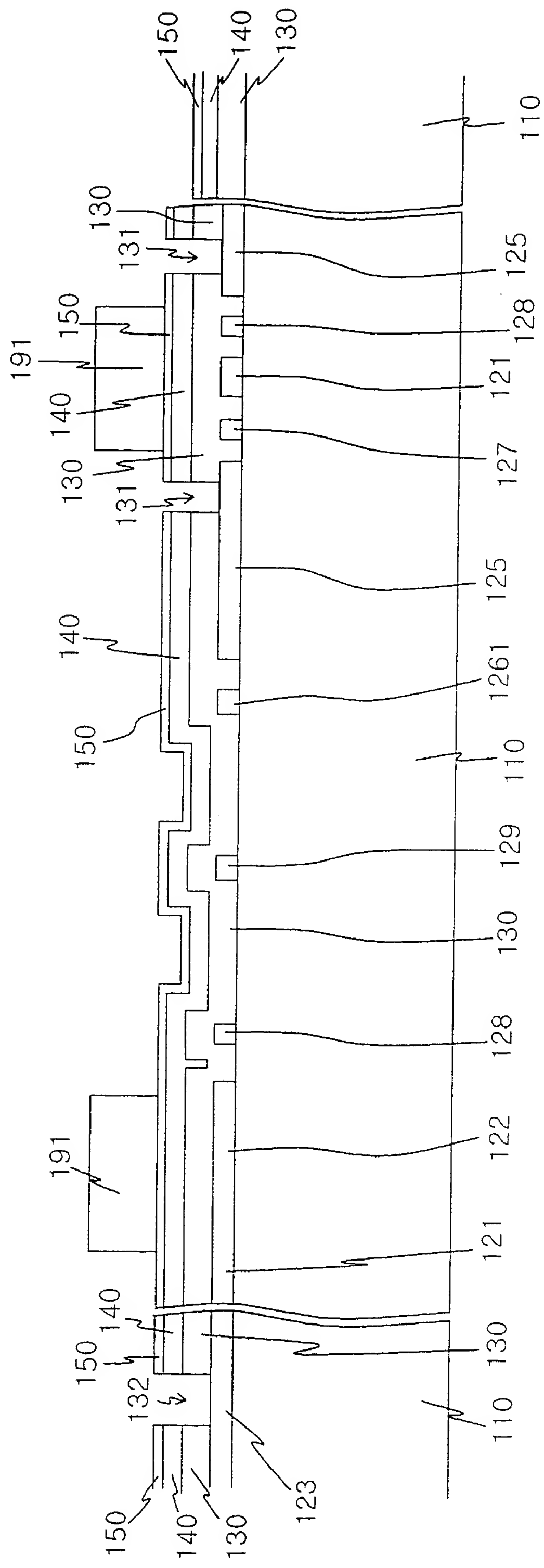


FIG.17

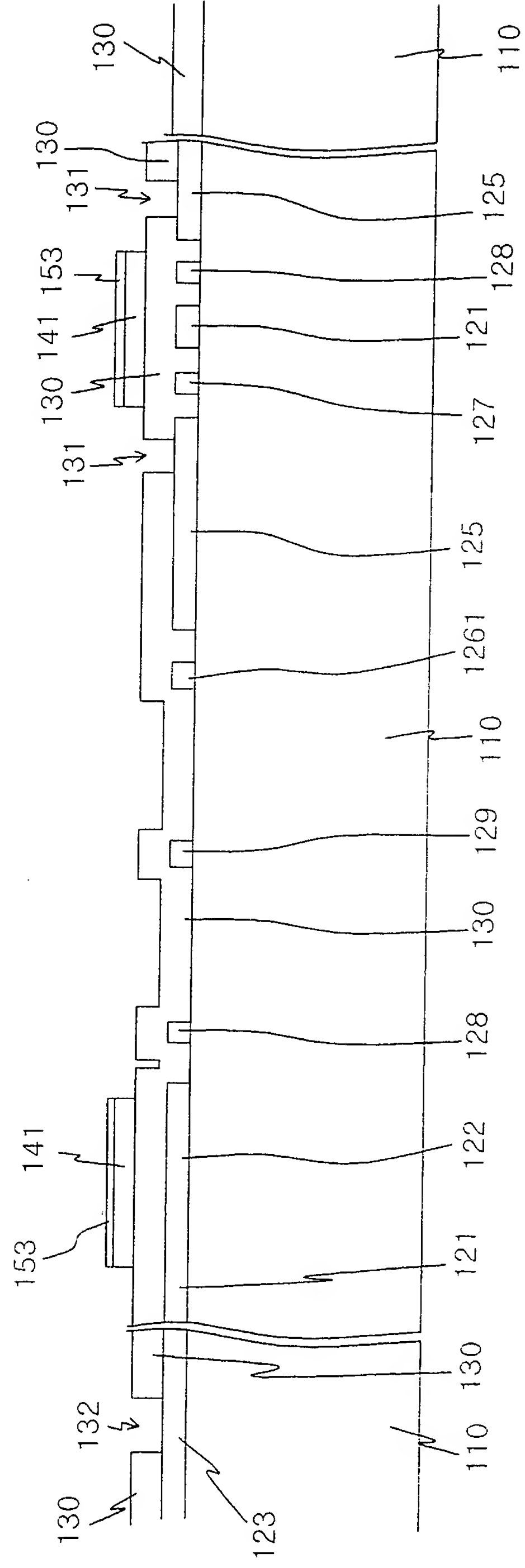


FIG. 18A

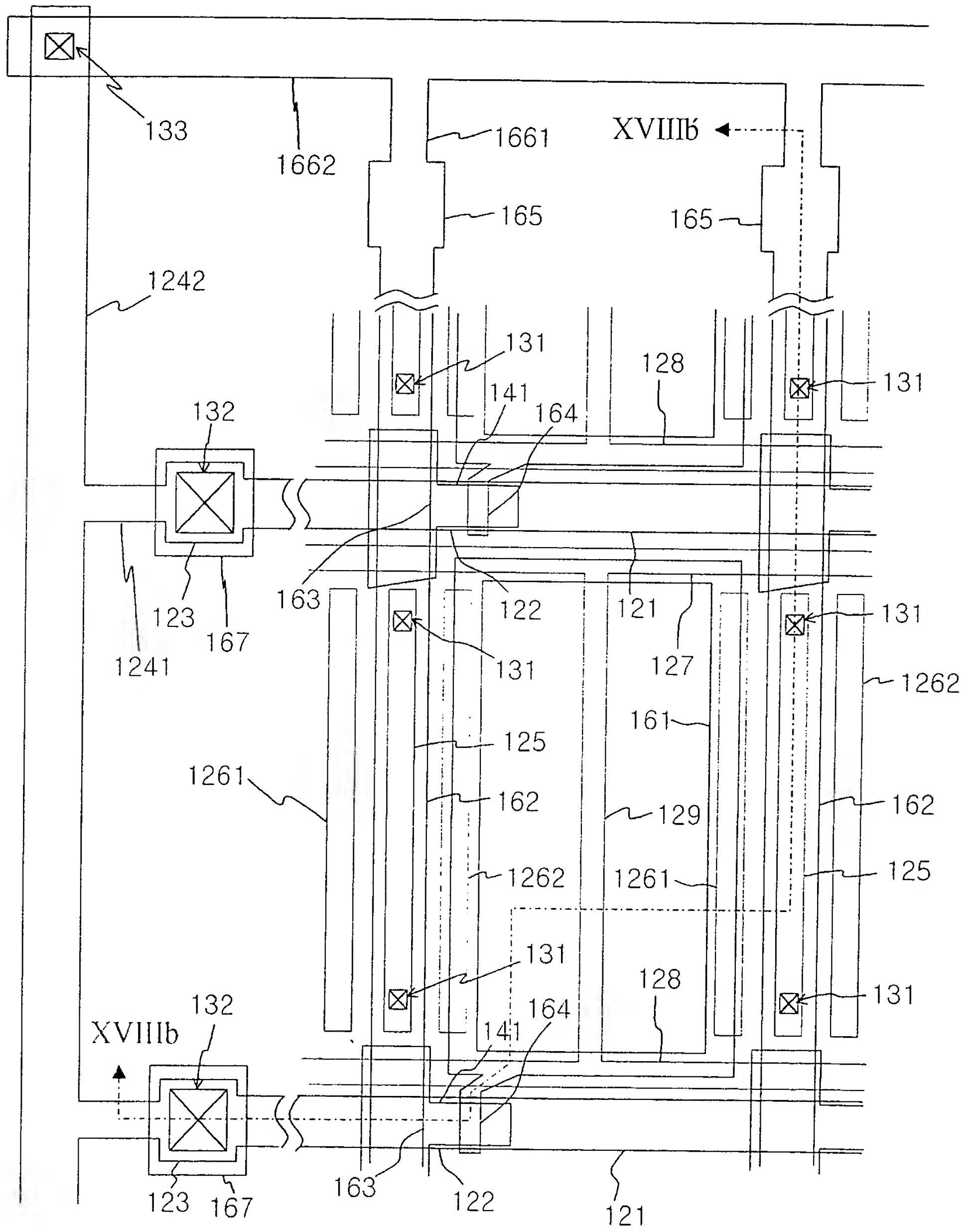


FIG.18B

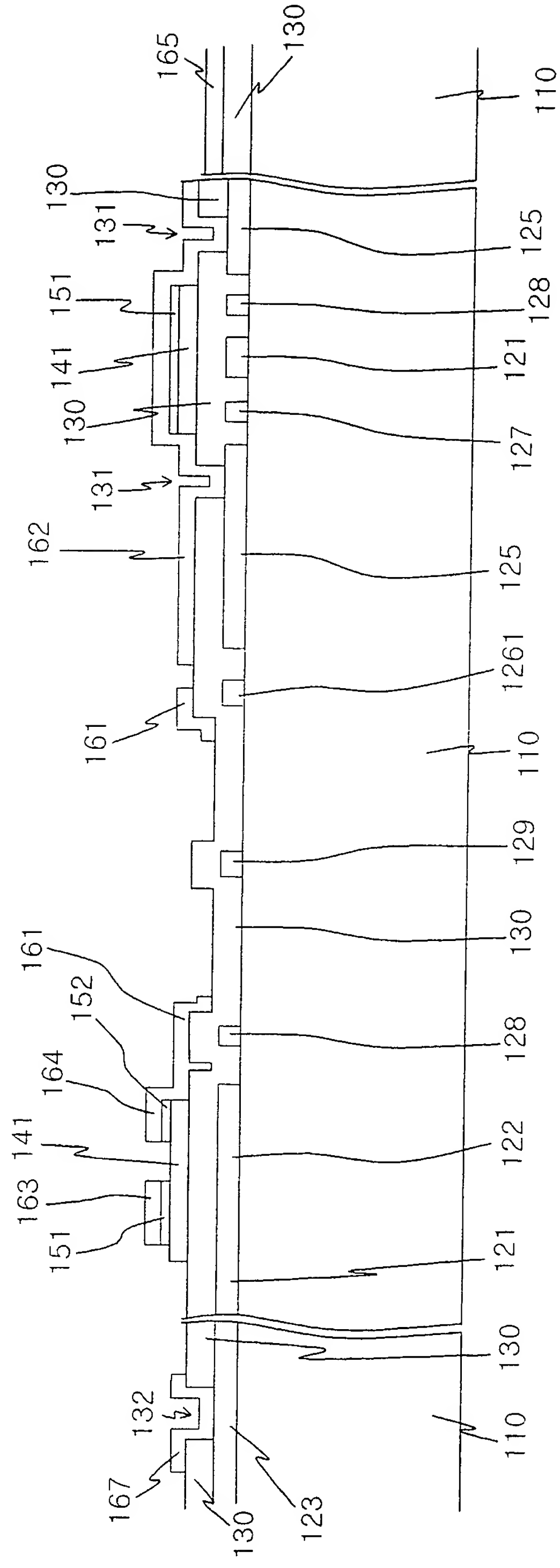


FIG. 19

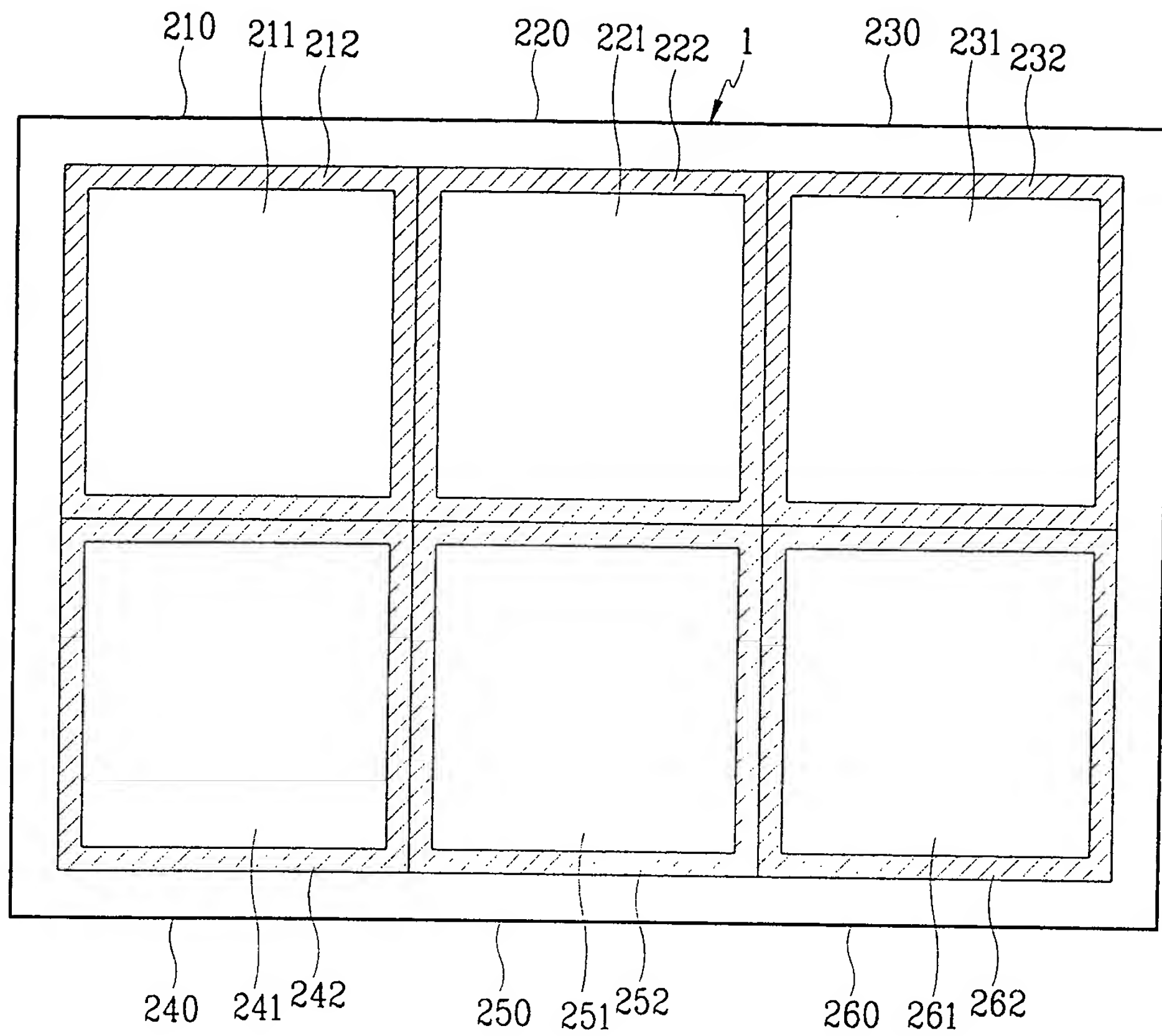


FIG. 20

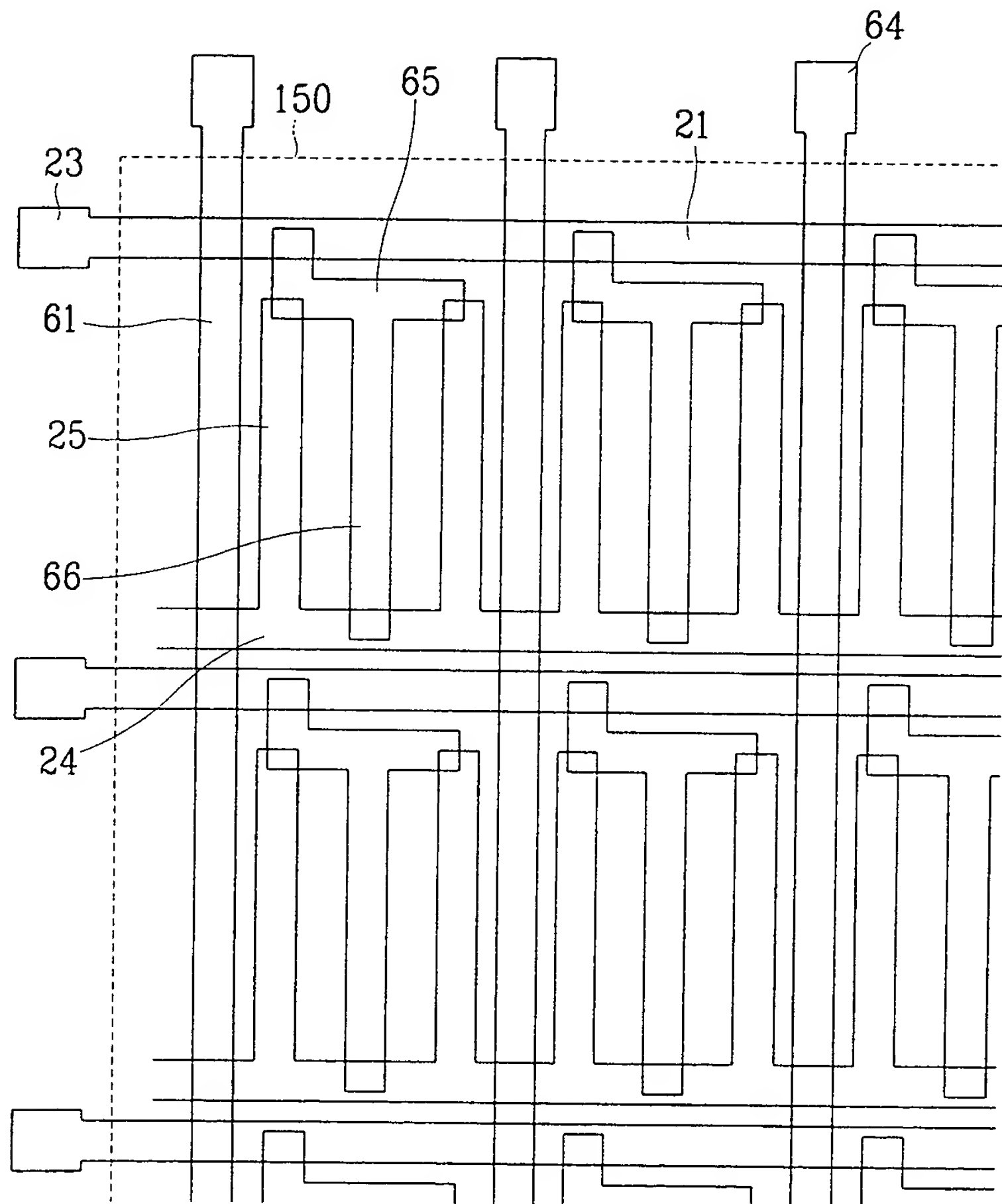




FIG. 21

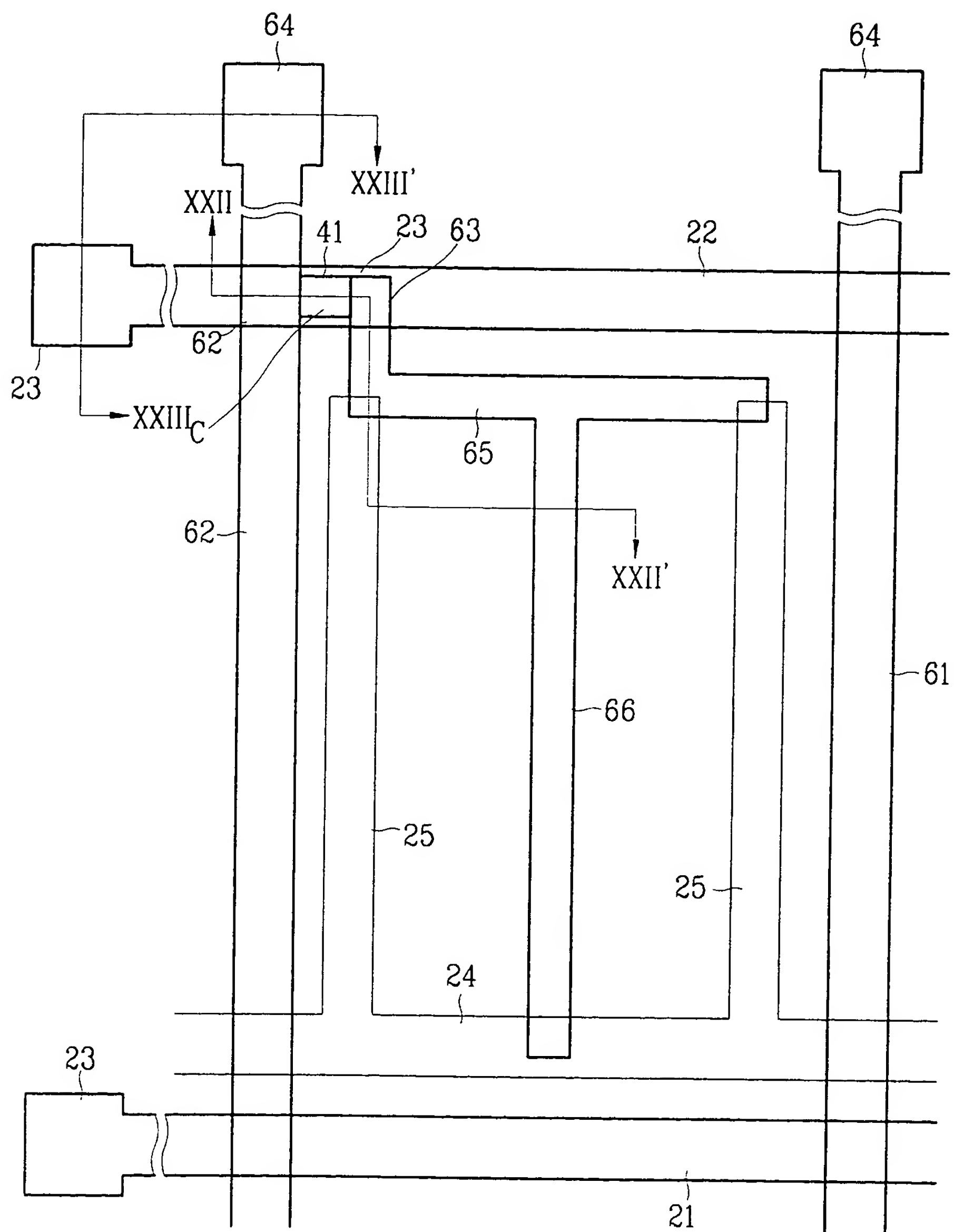


FIG. 22

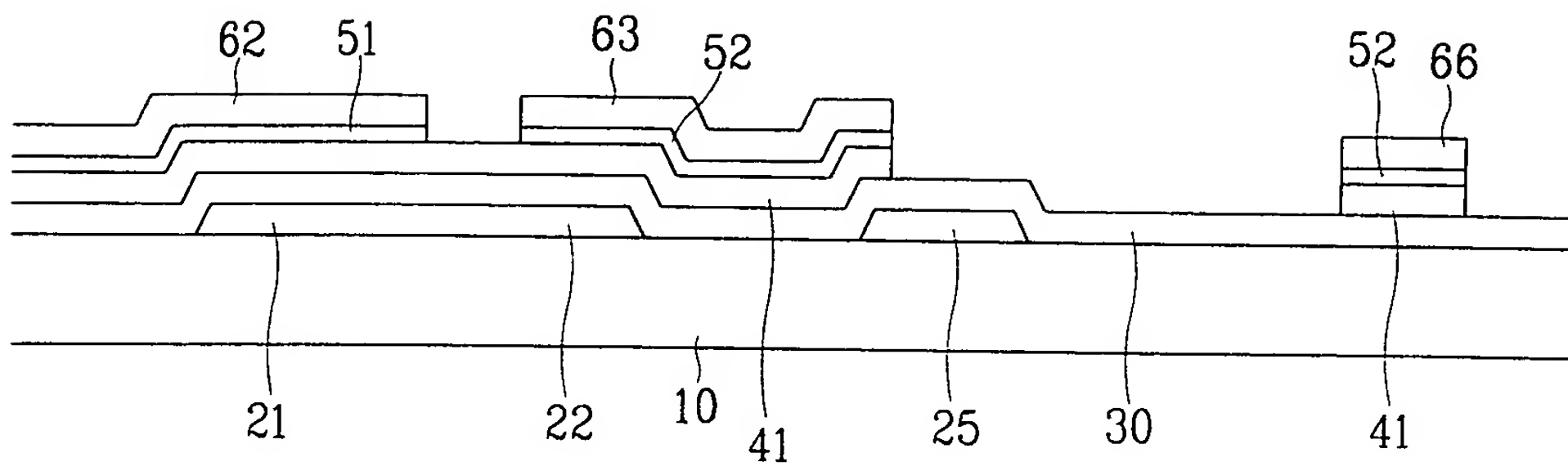


FIG. 23

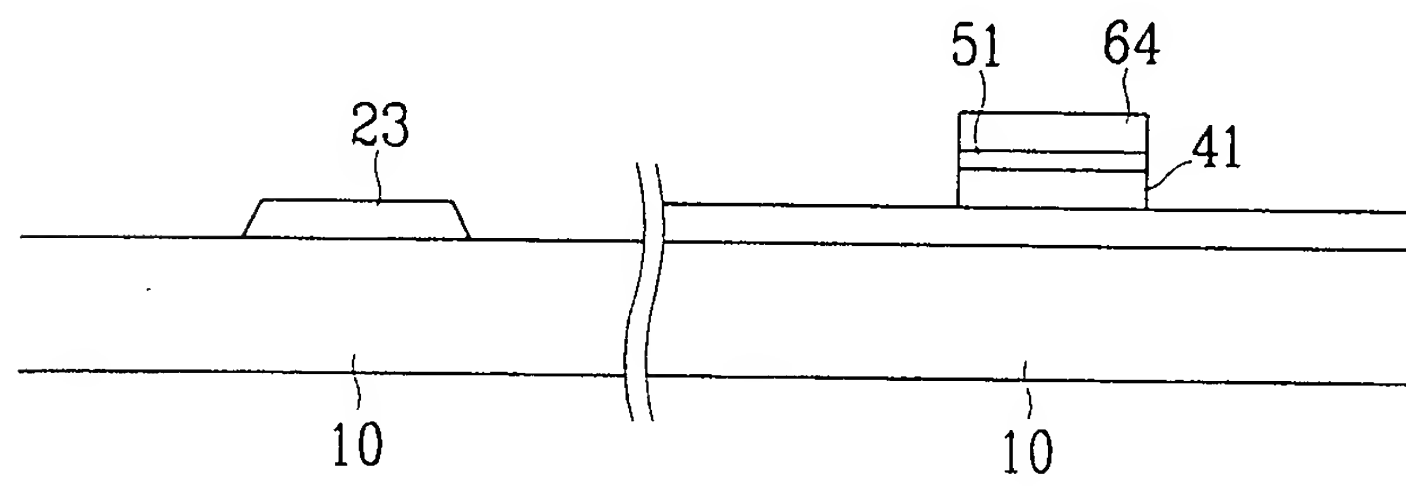
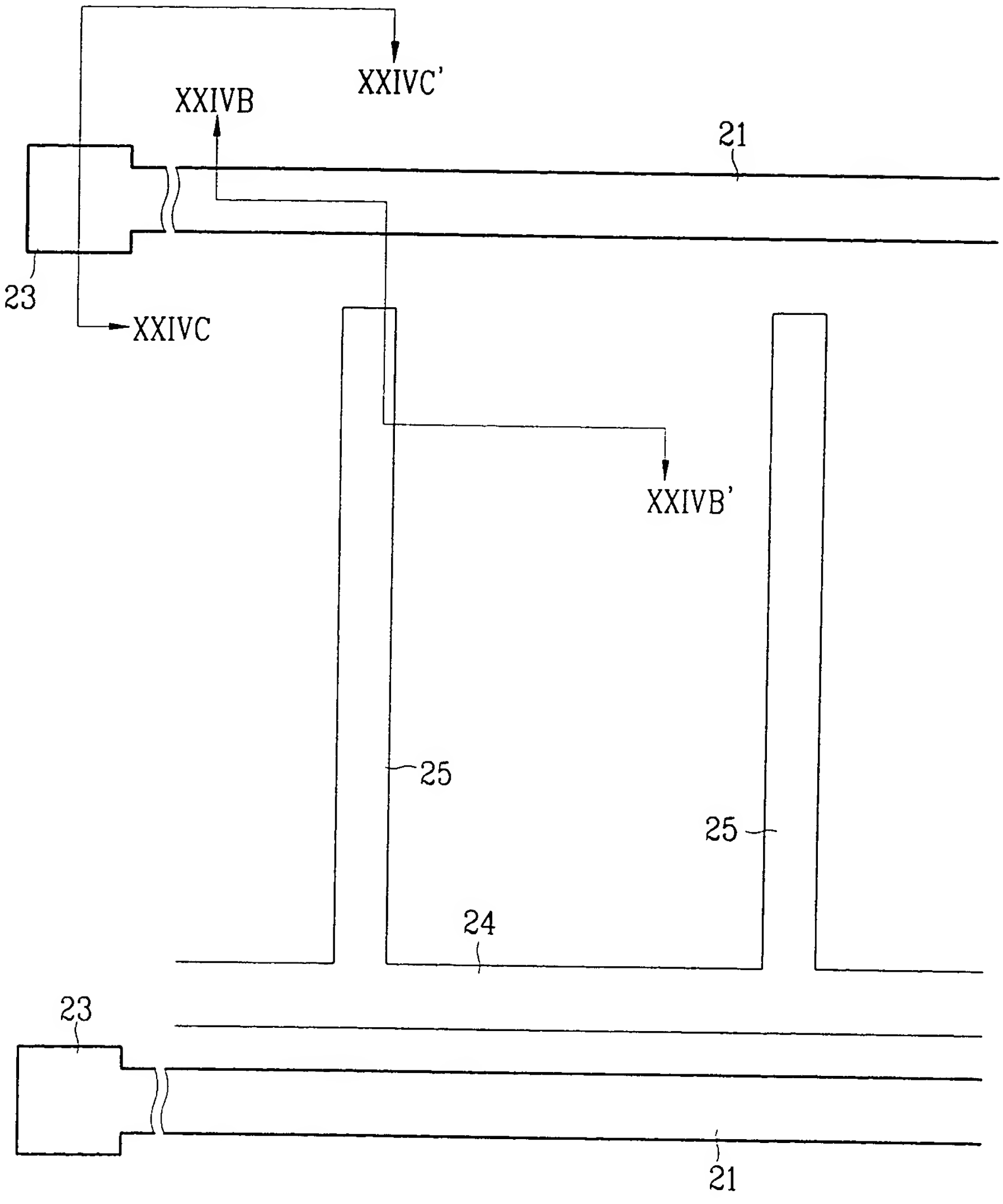
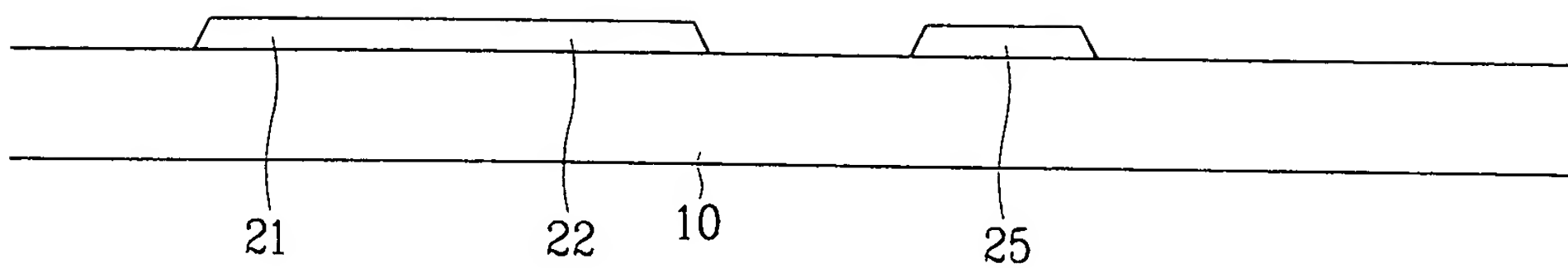


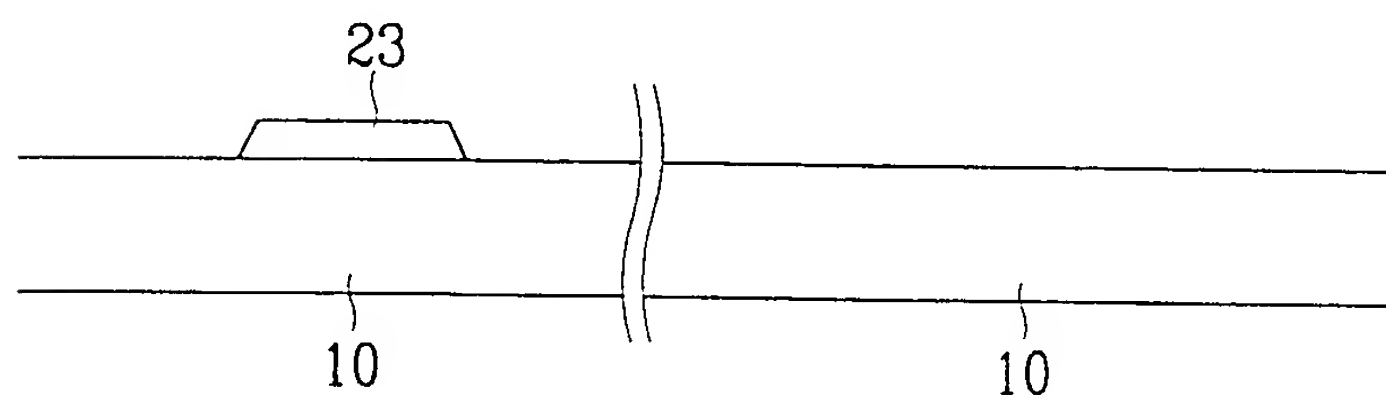
FIG. 24A



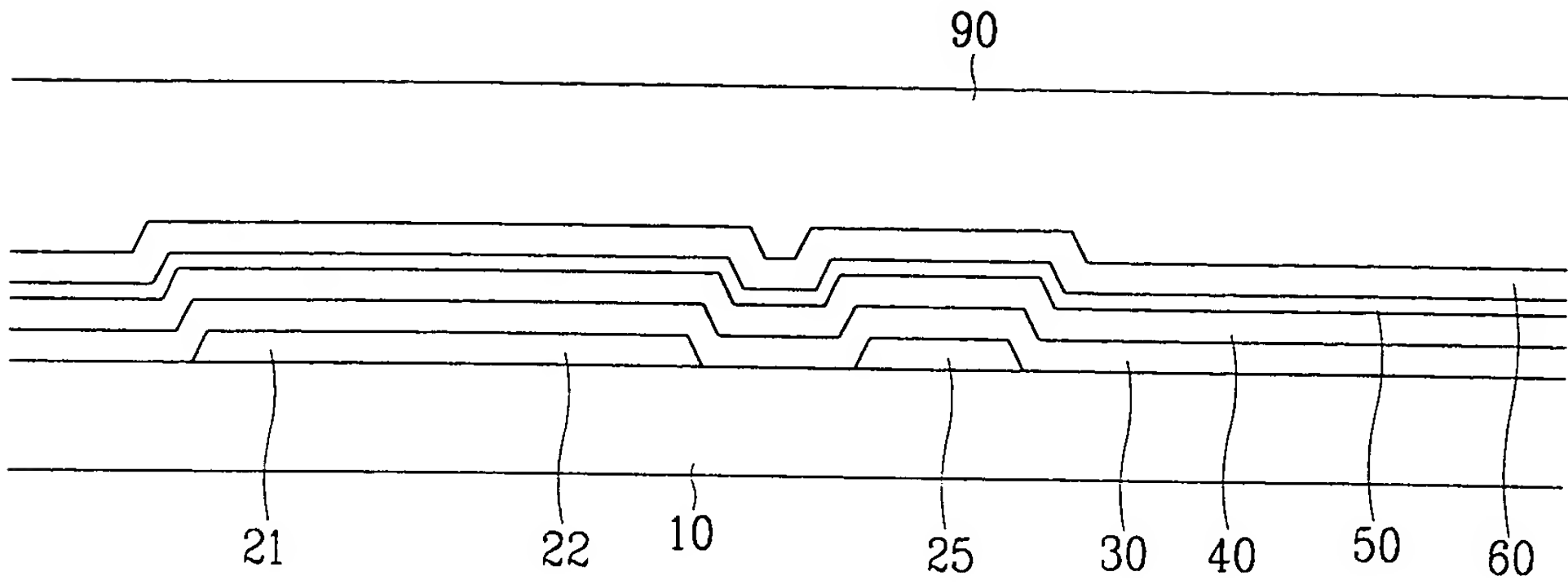
*FIG. 24B*



*FIG. 24C*



*FIG. 25A*



*FIG. 25B*

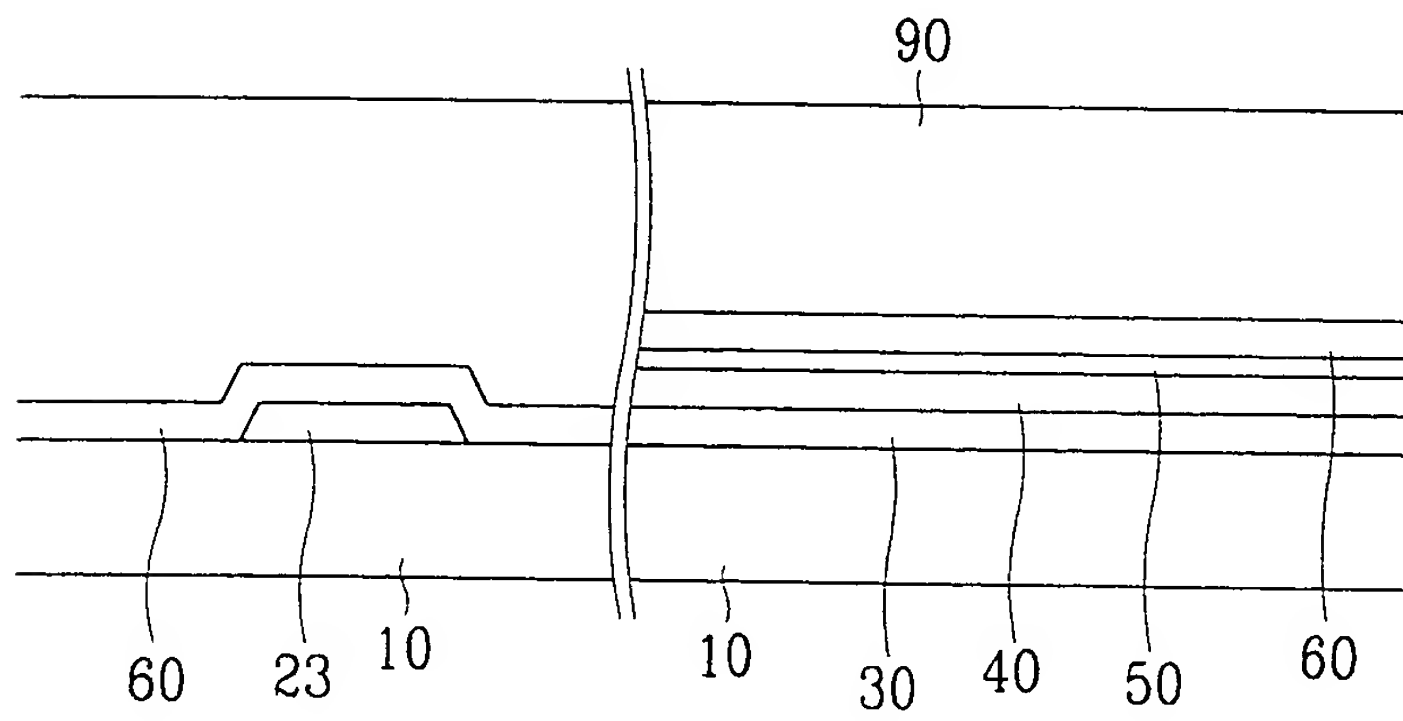


FIG. 26

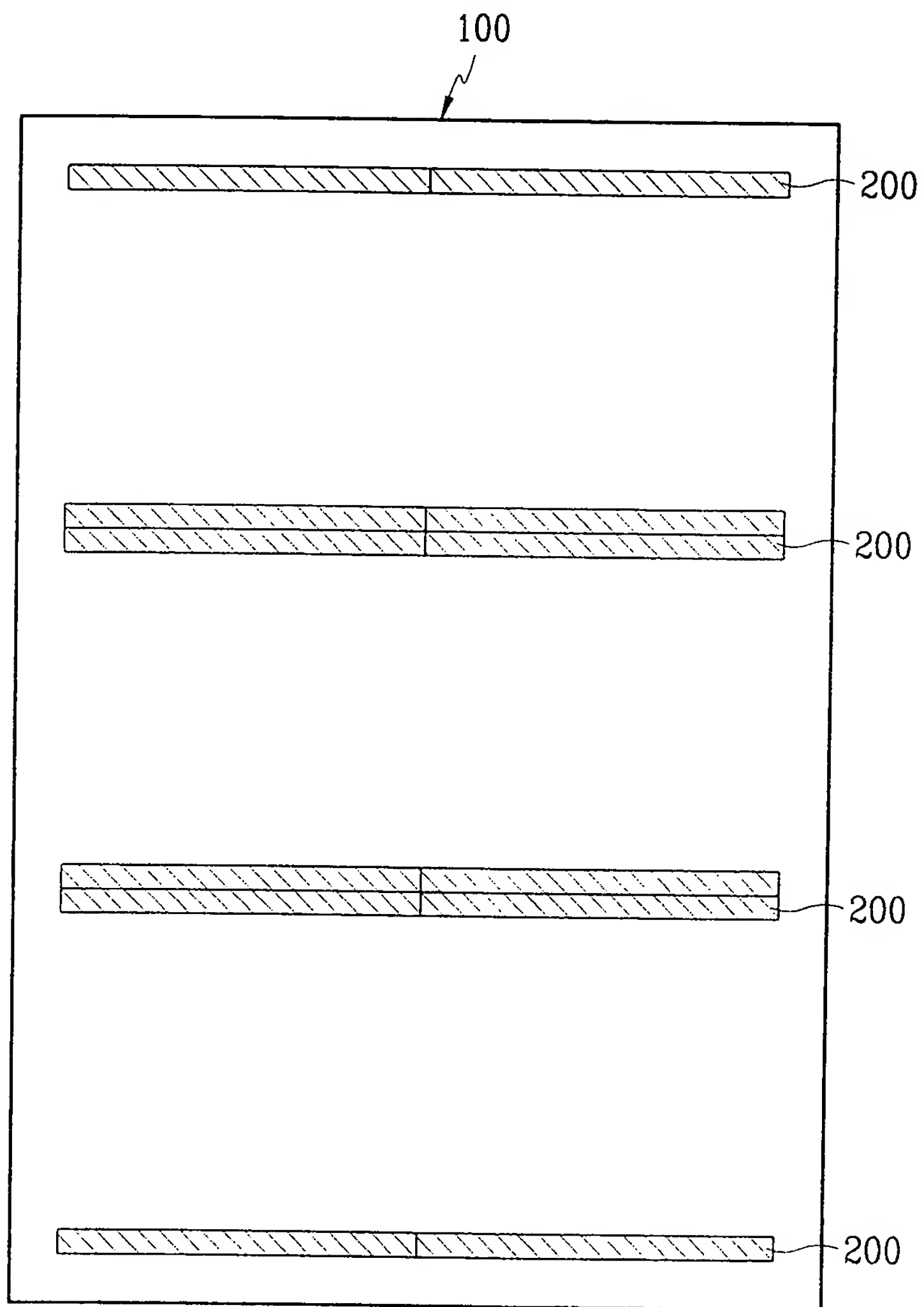


FIG. 27

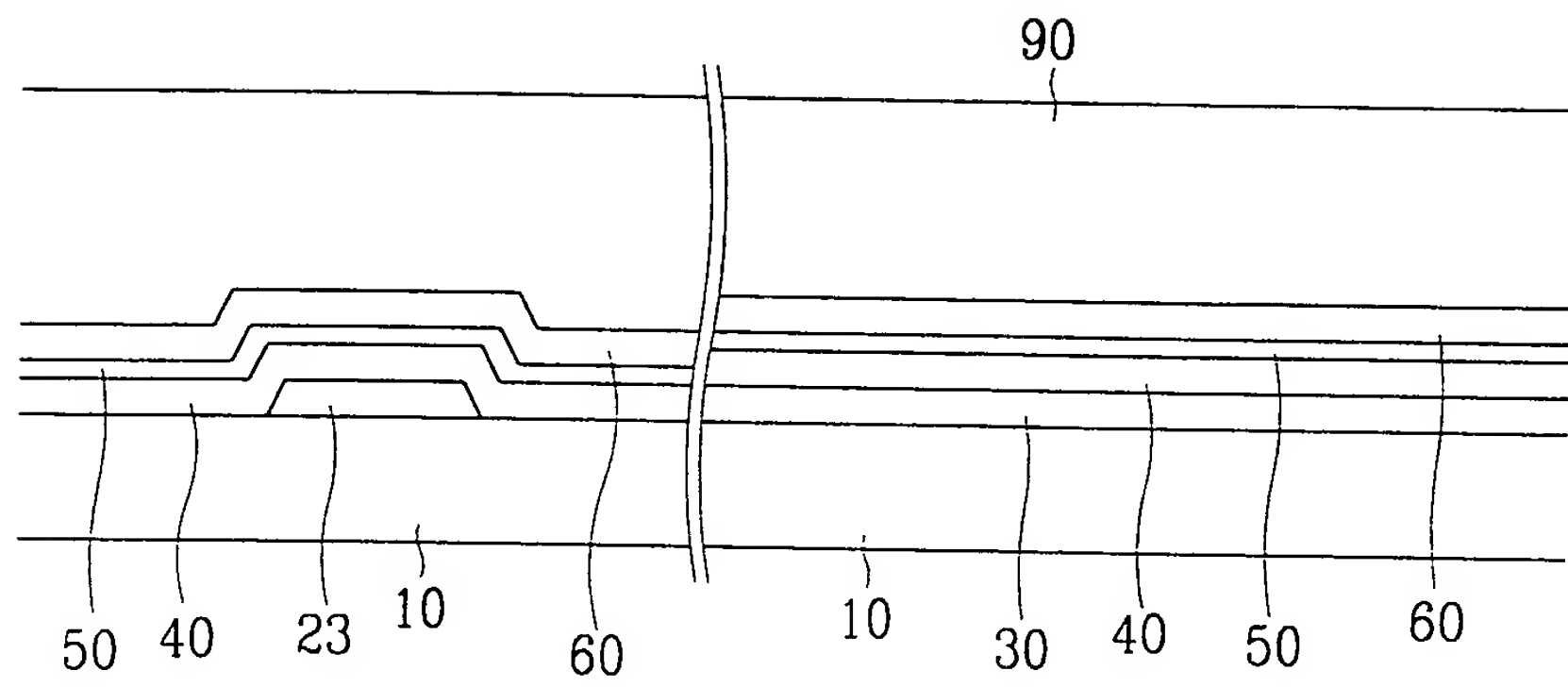


Figure 1 is a schematic diagram of a semiconductor device structure. The top part shows a plan view with regions labeled A, B, and C, and gates labeled 91 and 92. The bottom part shows a cross-sectional view with layers labeled 22, 26, 10, 28, 30, 40, 50, and 60. Vertical dashed lines connect the plan view to the cross-section.

This cross-sectional diagram illustrates a semiconductor device. On the left, a substrate consists of three horizontal layers labeled 60, 24, and 10 from bottom to top. A vertical layer, labeled 92, acts as a barrier or separator. To the right of layer 92, there is another set of layers: 30, 40, 50, and 60, stacked vertically. A rectangular feature, labeled 91, is positioned above the layer 30. At the very top, dimensions are indicated: 'B' spans the width of the left substrate, 'A' indicates the width of the rectangular feature 91, and another 'B' spans the width of the right substrate.



FIG. 29

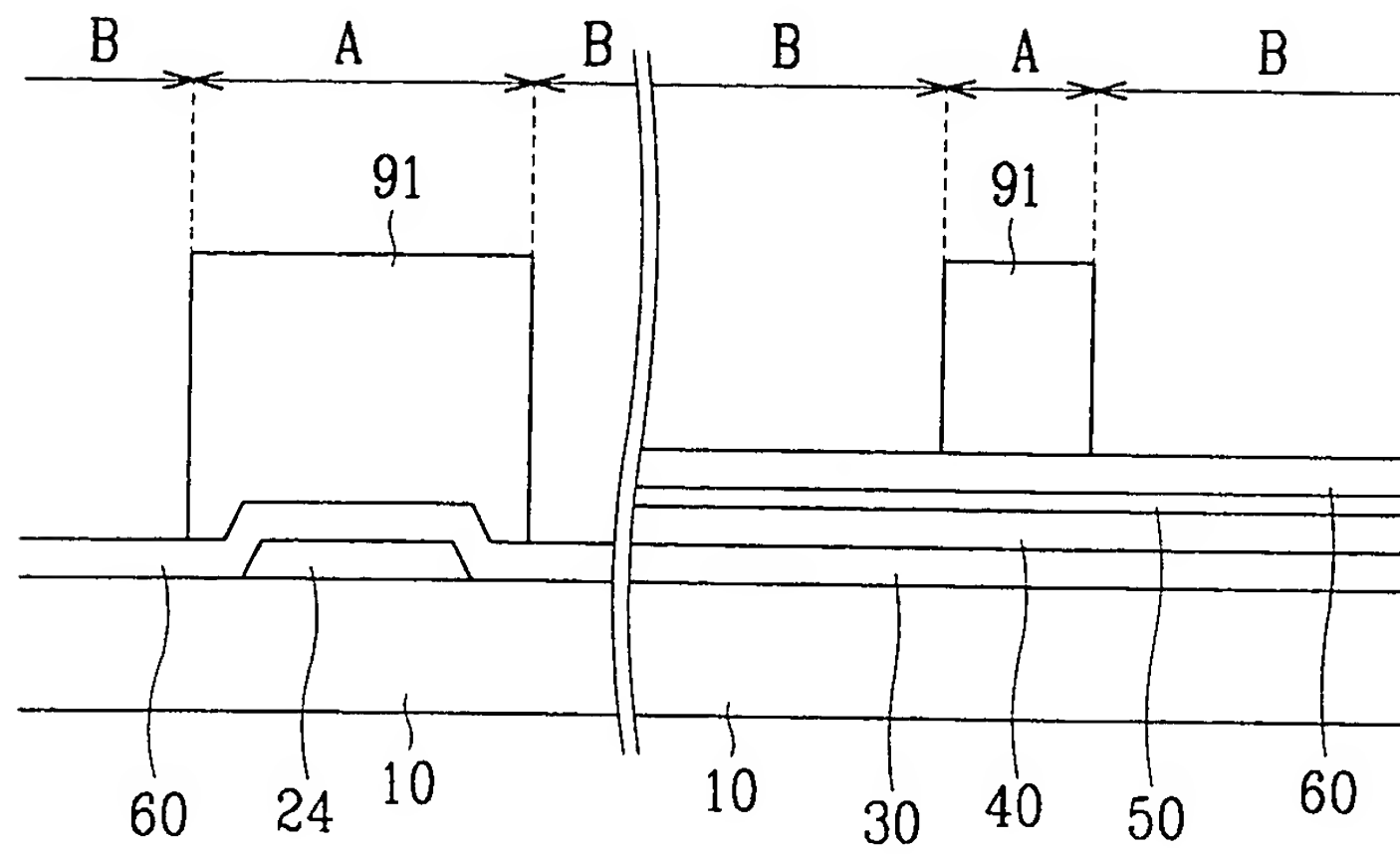


FIG. 30

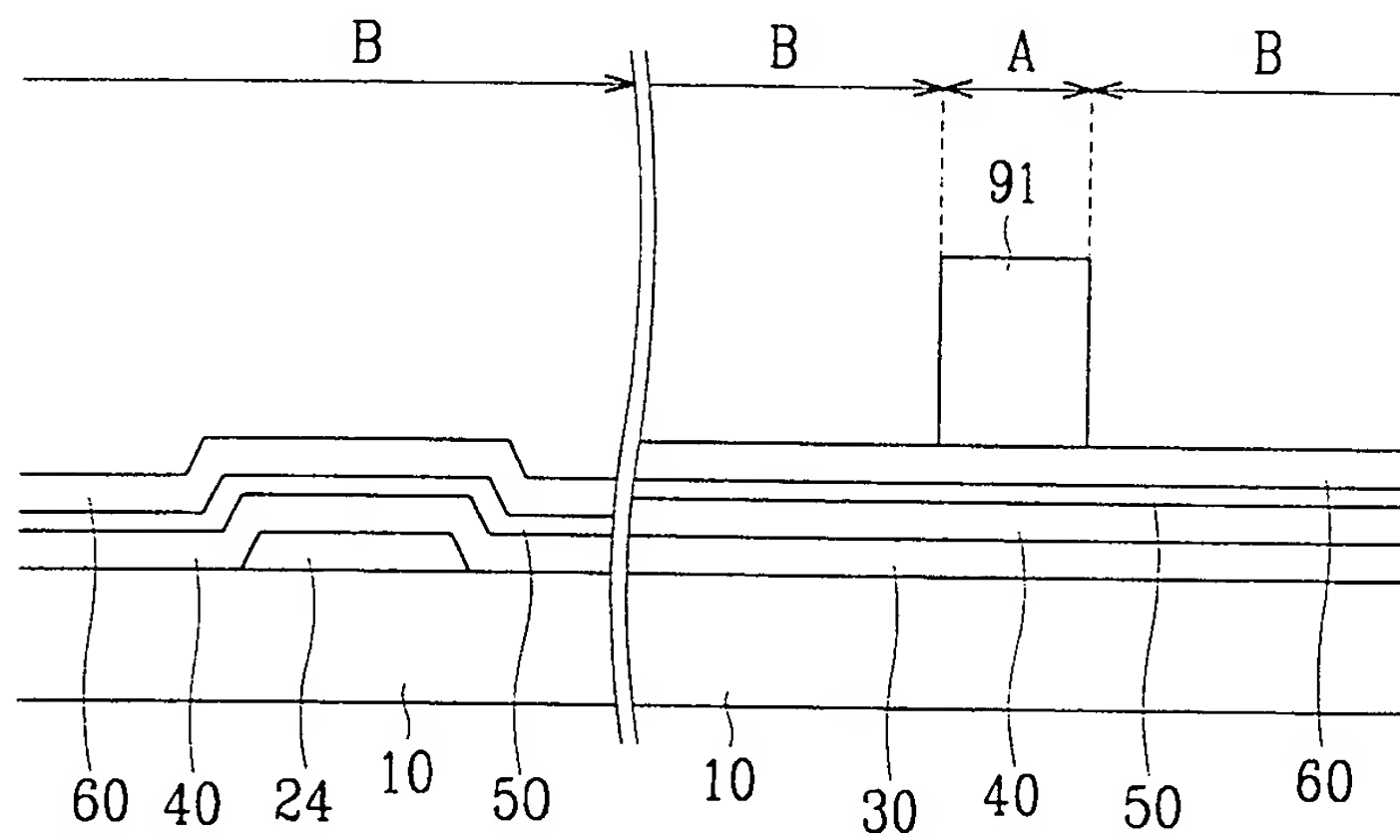


FIG. 31

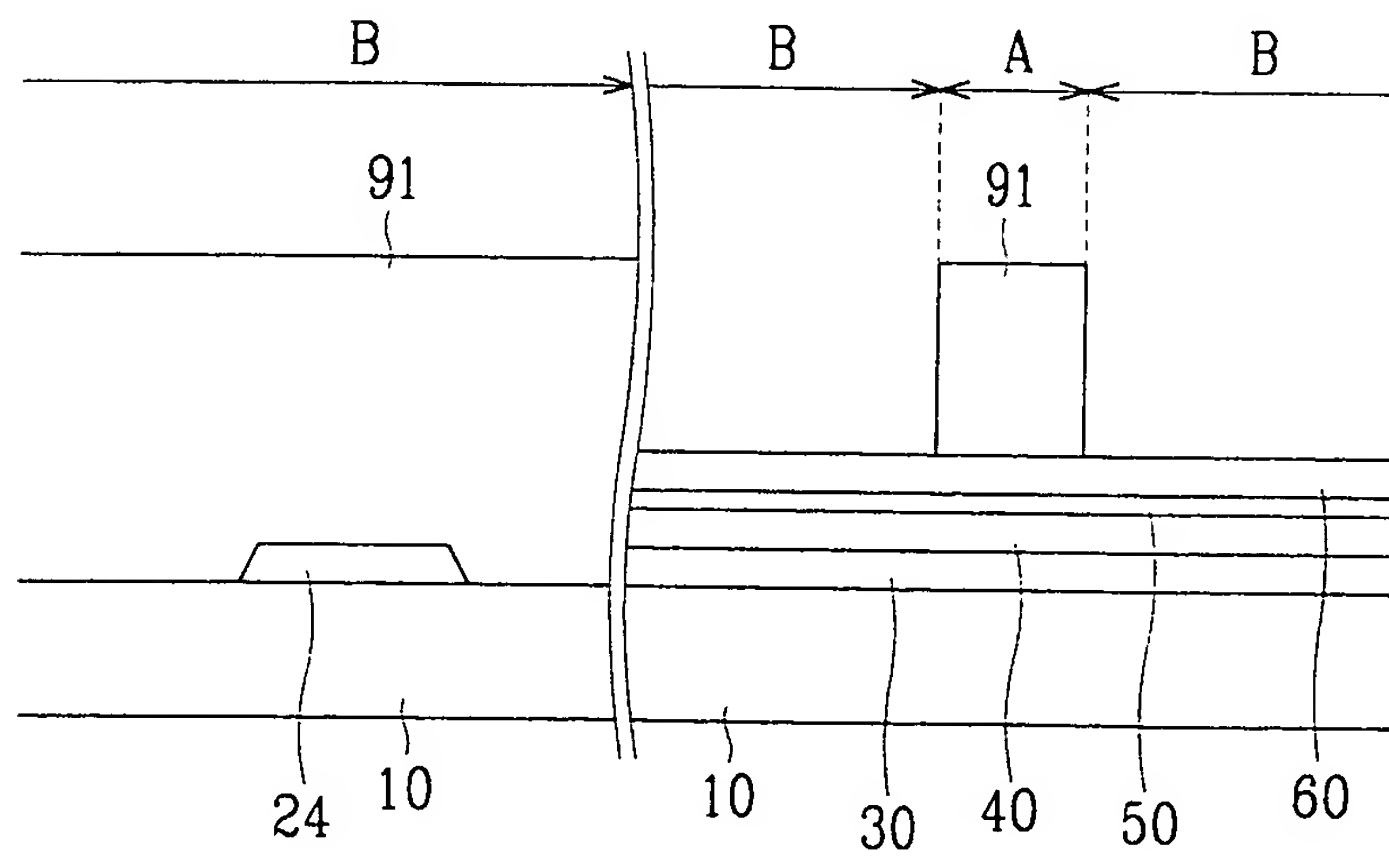


FIG. 32A

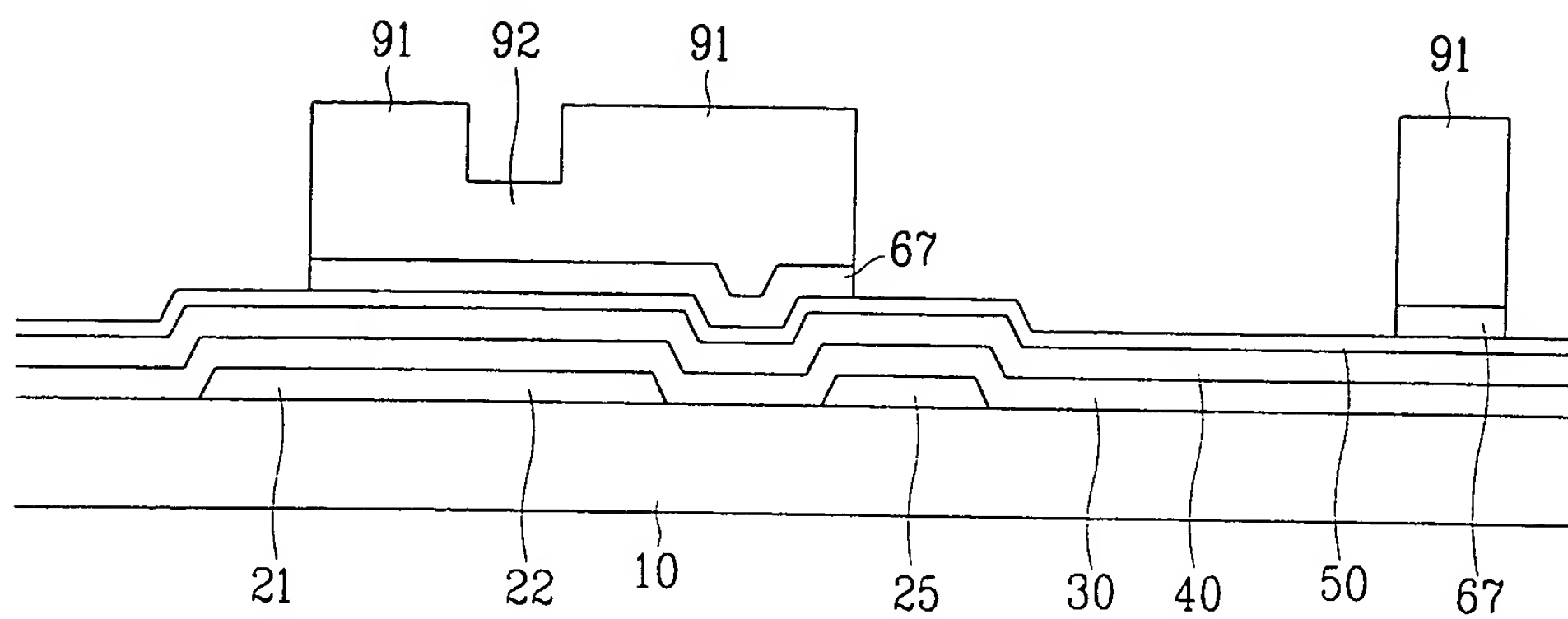
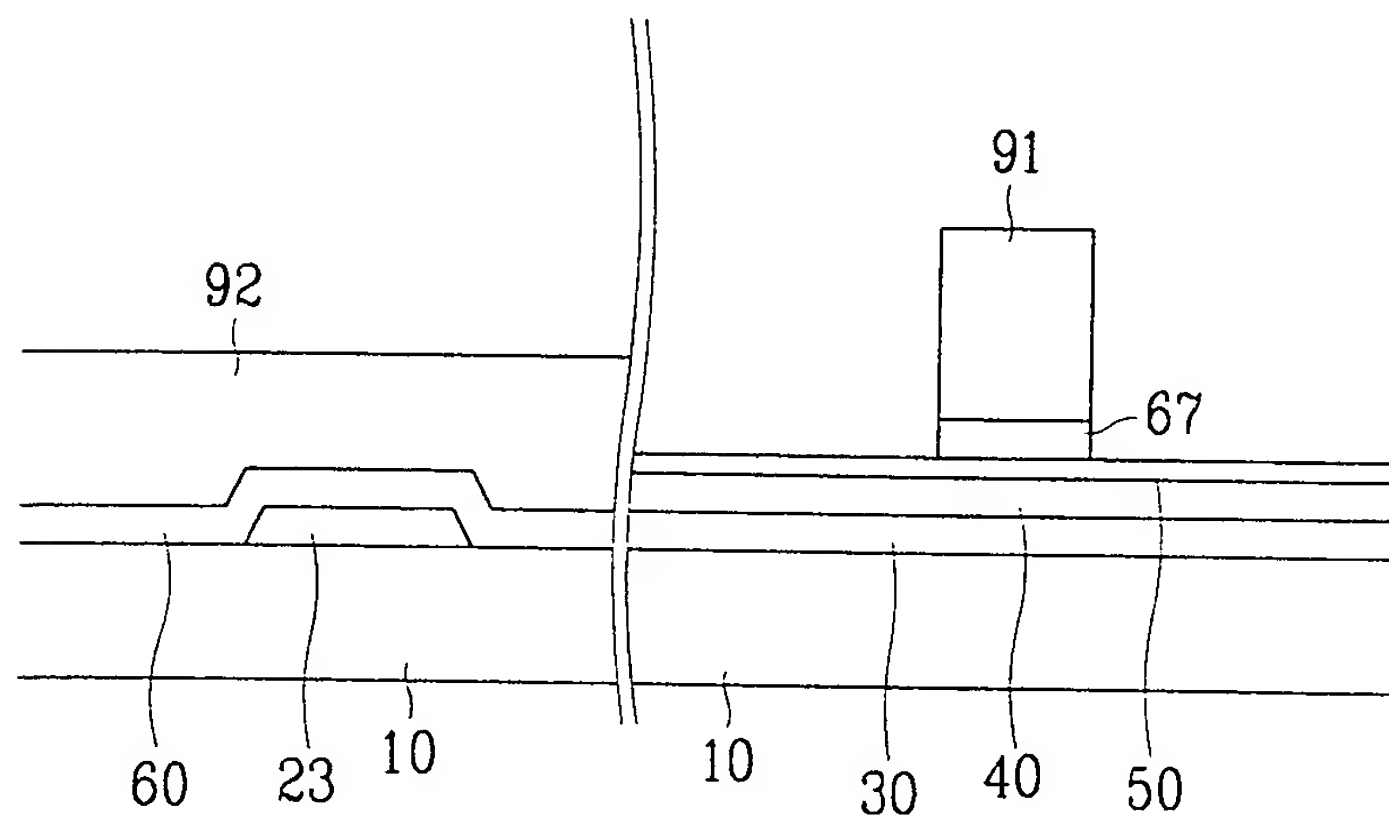
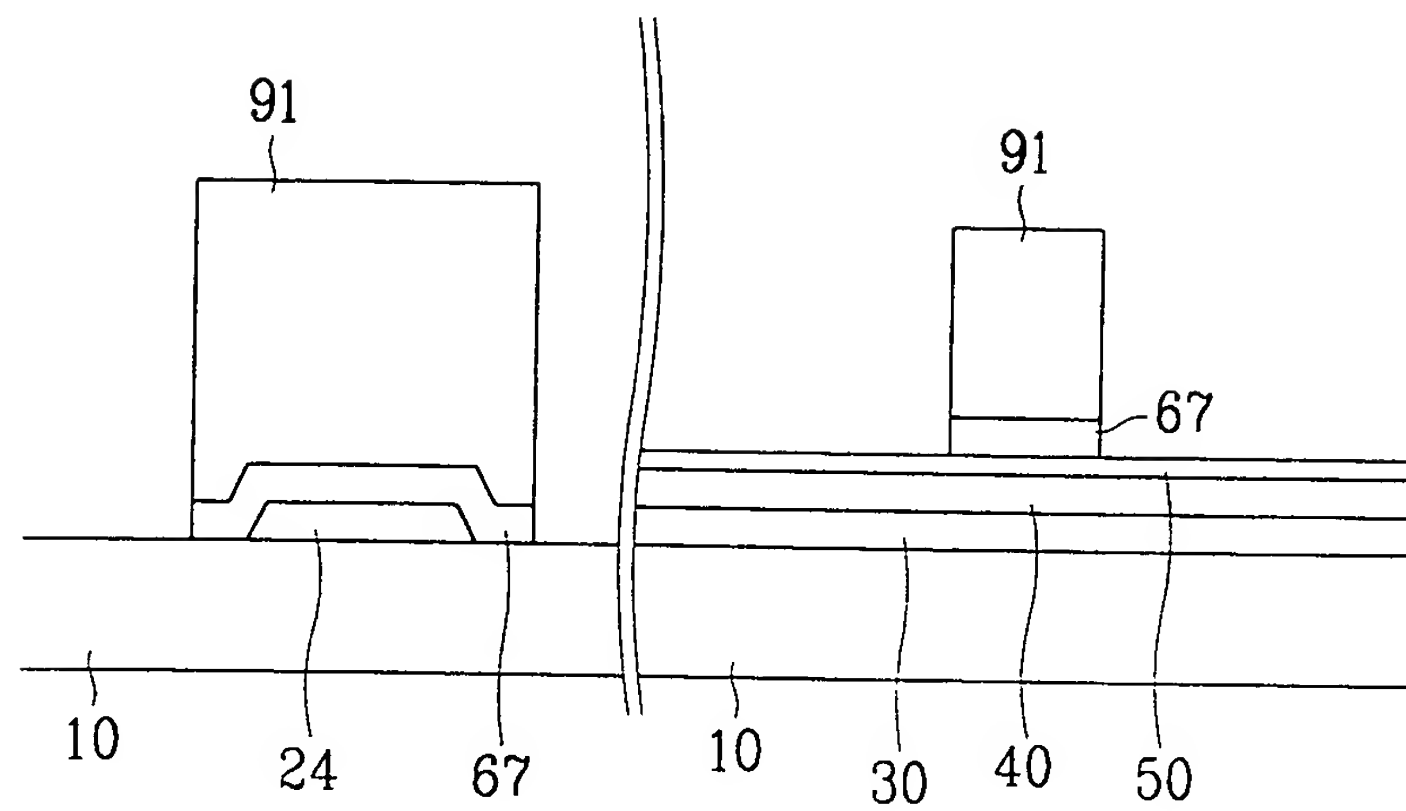


FIG. 32B



*FIG. 33A*



*FIG. 33B*

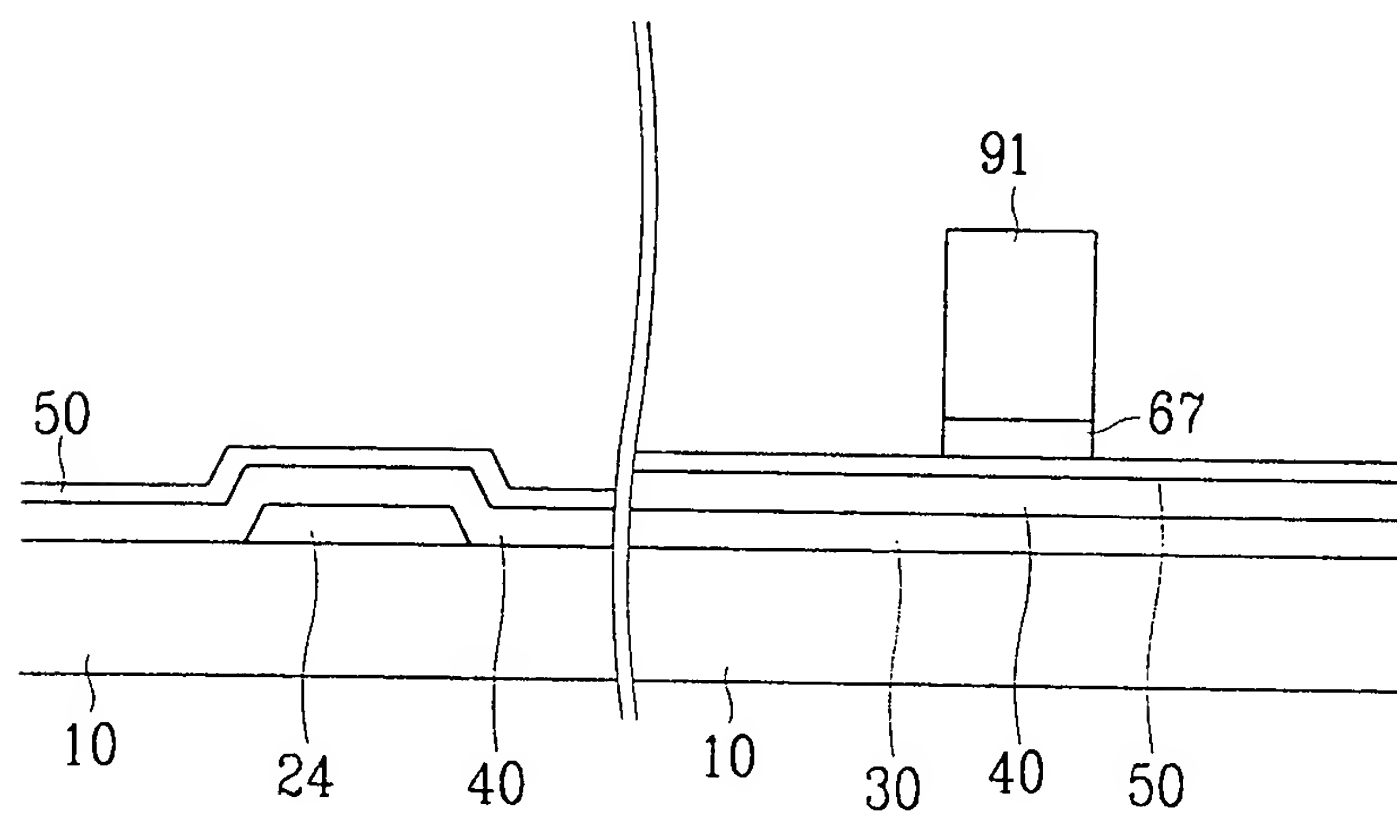


FIG. 34A

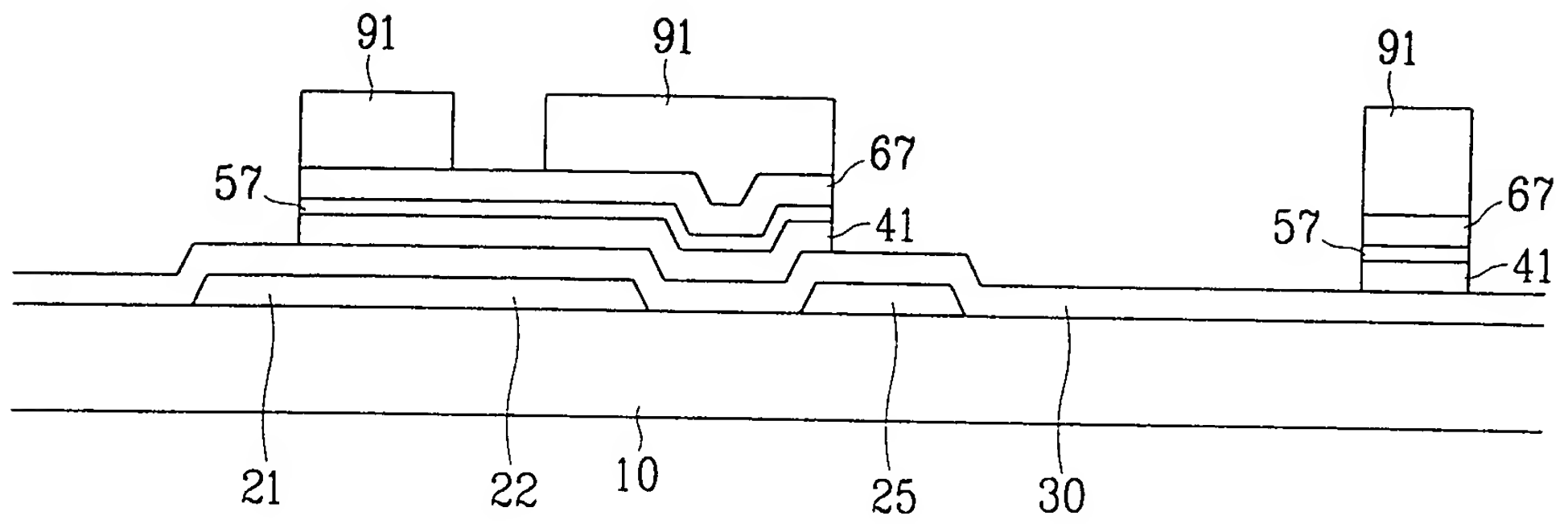


FIG. 34B

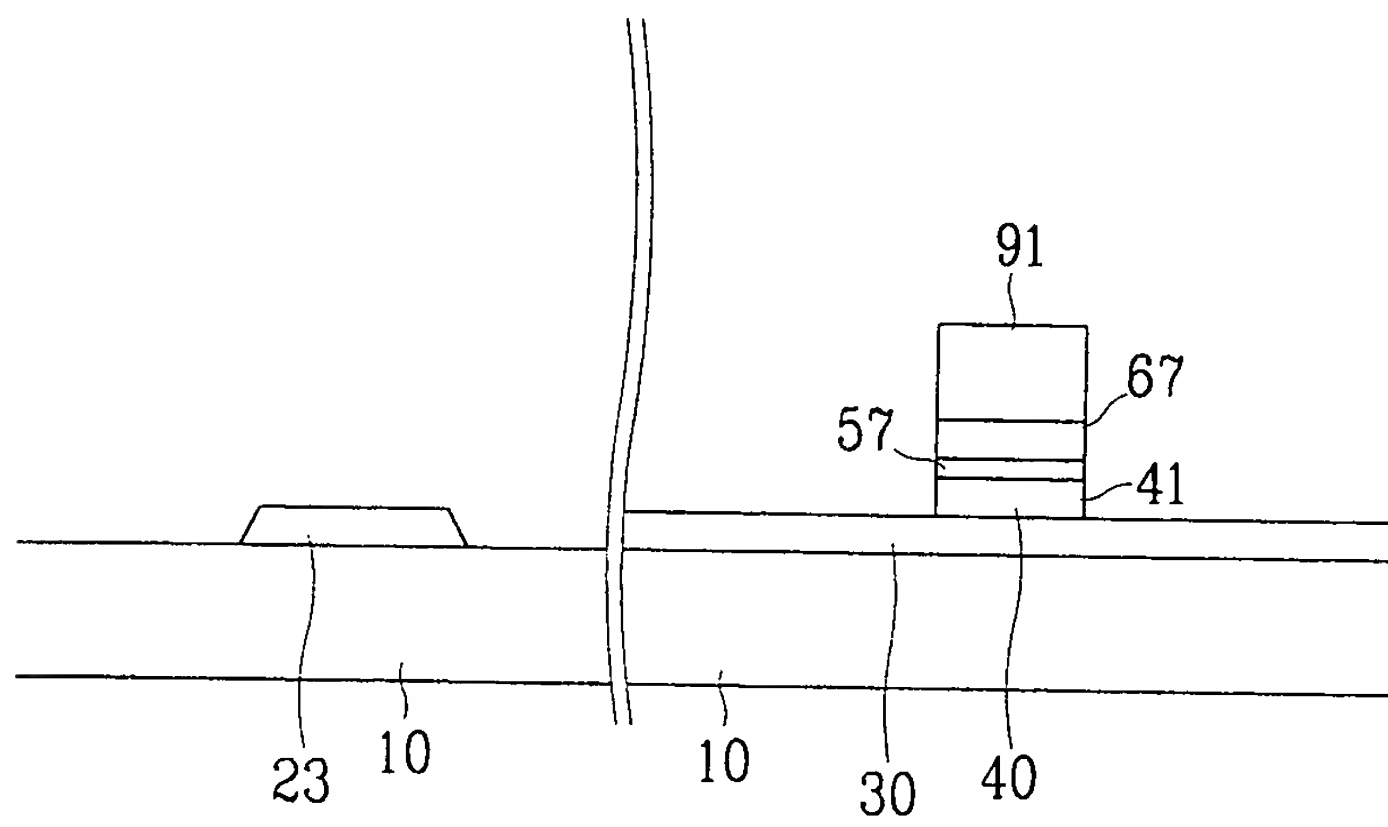


FIG. 35A

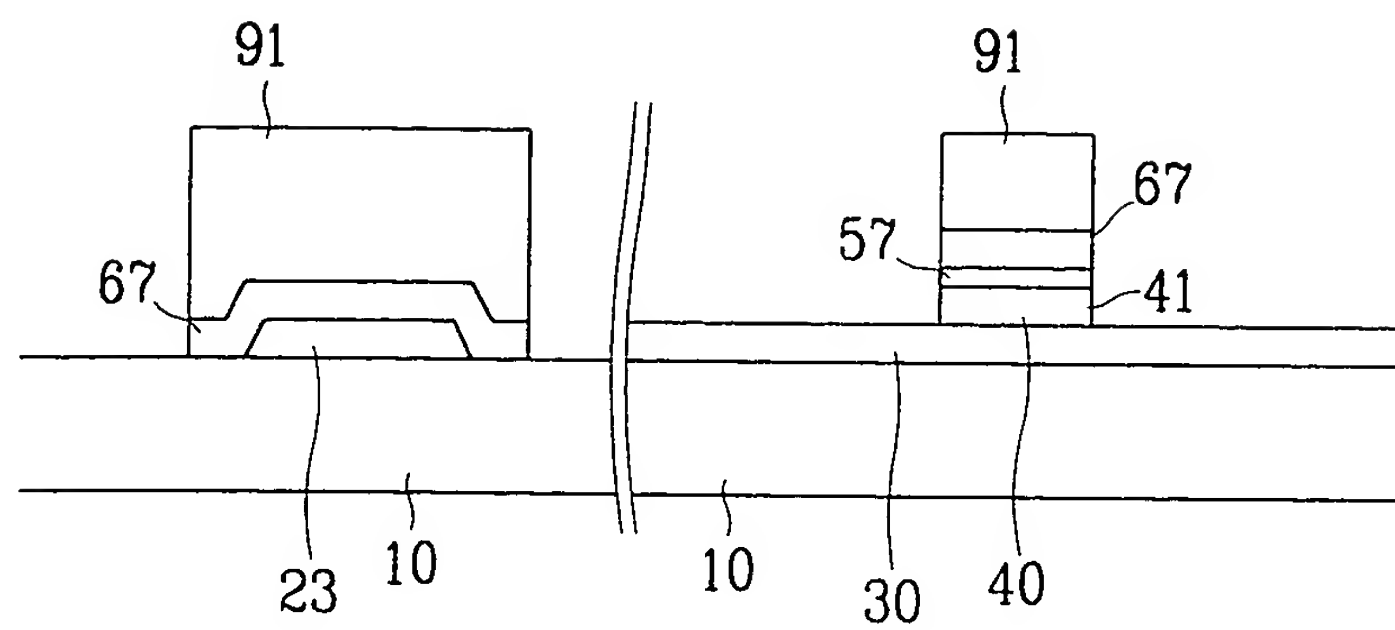


FIG. 35B

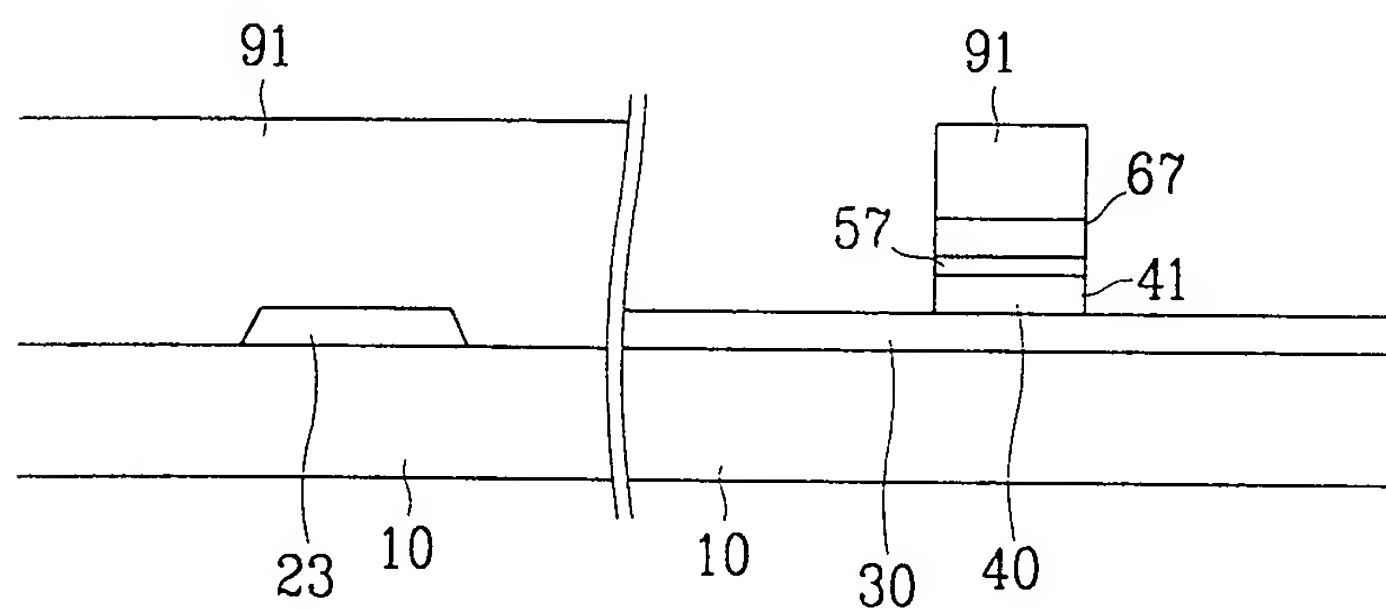


FIG. 35C

